

# MoVeIT strip silicon detectors for proton beam monitoring: preliminary results



A Vignati<sup>1</sup>, V Monaco<sup>1,2</sup>, A Attili<sup>1</sup>, M Boscardin<sup>3</sup>, N Cartiglia<sup>1</sup>, GF Dalla Betta<sup>4</sup>, M Donetti<sup>5</sup>, F Fausti<sup>1,6</sup>, M Ferrero<sup>1</sup>, F Ficarella<sup>3</sup>, S Giordanengo<sup>1</sup>, O Hammad Ali<sup>1,2</sup>, M Mandurrino<sup>1</sup>, L Manganaro<sup>1,2</sup>, G Mazza<sup>1</sup>, L Pancheri<sup>4</sup>, G Paternoster<sup>3</sup>, R Sacchi<sup>1,2</sup>, Z Shakarami<sup>2</sup>, V Sola<sup>1</sup>, A Staiano<sup>1</sup>, R Cirio<sup>1,2</sup>

1 – INFN - National Institute for Nuclear Physics - Torino, 2 – Università degli Studi di Torino, 3 – Fondazione Bruno Kessler (FBK), 4 – Università degli Studi di Trento, 5 – Fondazione CNAO, 6 – Polytechnic University of Turin

# Aim of the project

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**M**odeling and **V**erification for  
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For additional details <http://www.tifpa.infn.it/projects/move-it/>

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Implementation of advanced radiobiological models in  
ion TPS, experimental verification in-vitro and in-vivo.

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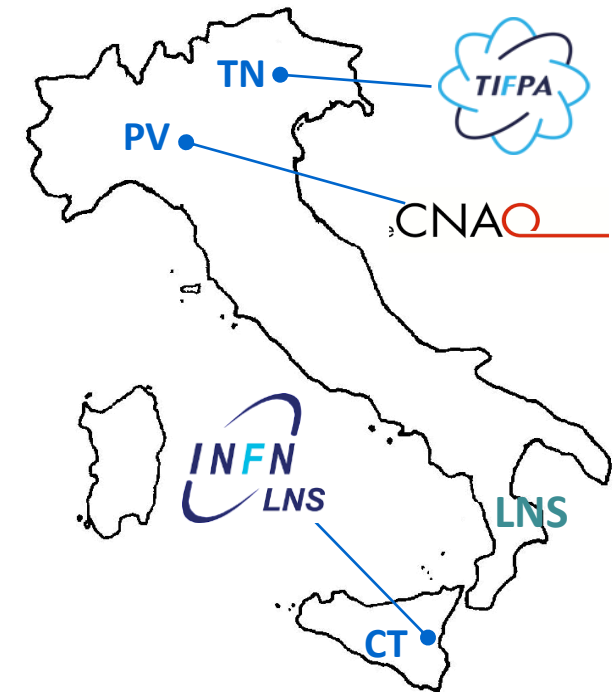
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**Two prototypes of UFSD for radiobiological applications @ three irradiation facilities:**



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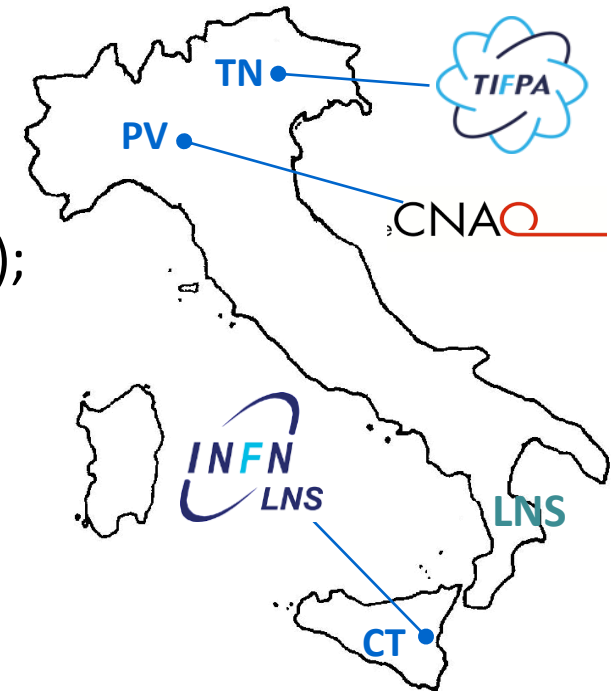


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**Two prototypes of UFSD for radiobiological applications @ three irradiation facilities:**

1. to **directly count** individual protons:

- area  $3 \times 3 \text{ cm}^2$ ;
- up to fluence rate of  $10^8 \text{ p/s cm}^2$  (with error  $< 1\%$  - clinical requirement);
- segmented in strips  $\rightarrow$  beam projections in two orthogonal directions;



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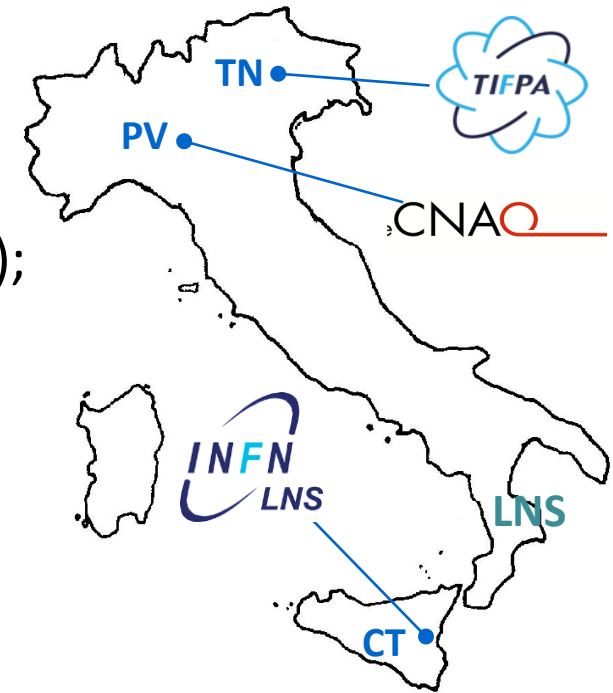
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  - segmented in strips  $\rightarrow$  beam projections in two orthogonal directions;
2. to **measure the beam energy** with time-of-flight techniques, using a telescope of two UFSD sensors:
  - error  $< 1 \text{ mm}$  range in water.

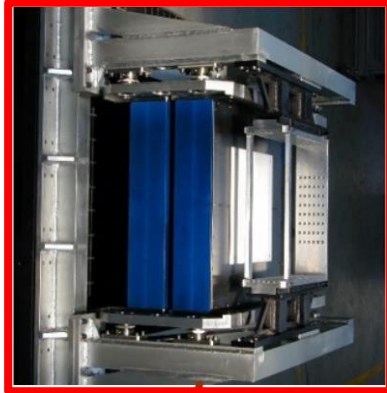
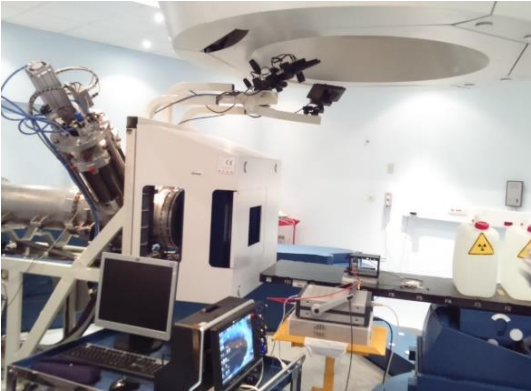


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# Motivation: beam monitoring in PT

Gas detectors (e.g. ionization chambers)  
common choice for existing therapy centers

CNAO



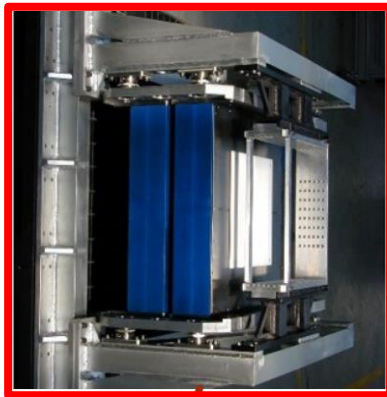
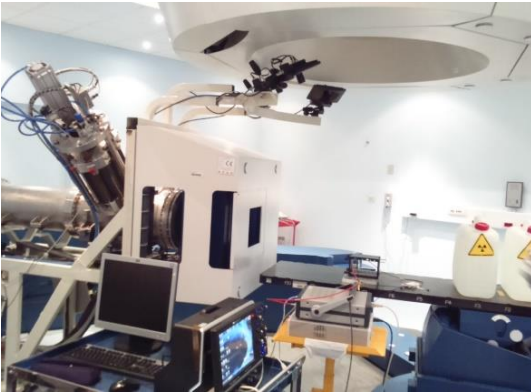
✓ Large area;  
robust and stable;  
radiation resistant,  
limited water  
equivalent  
thickness.

✗ Slow charge  
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limited sensitivity.

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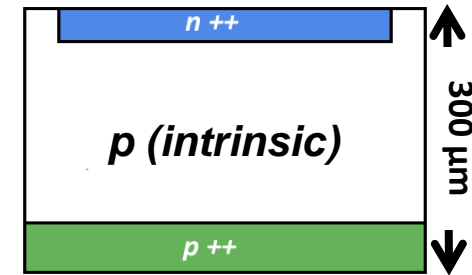
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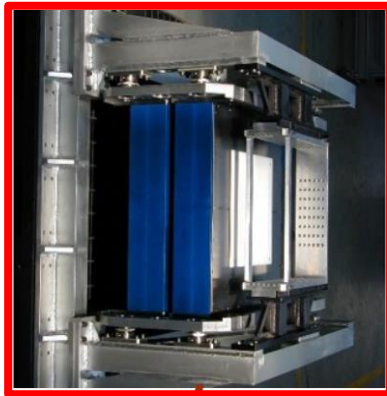
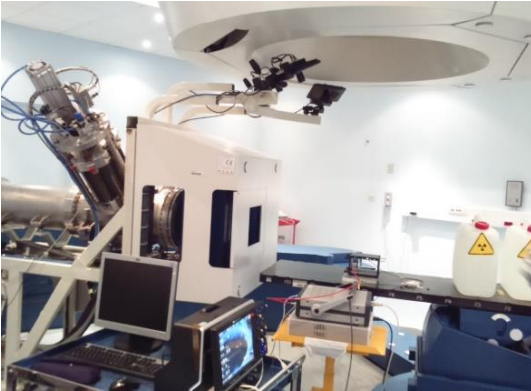
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Large granularity.

✗ Higher readout  
complexity;  
Radiation damage;  
Pile-up effects.

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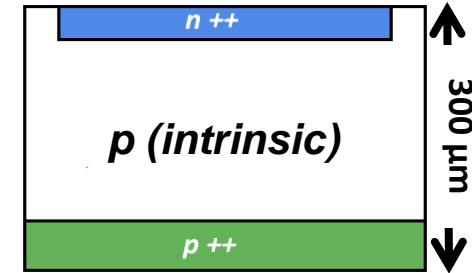
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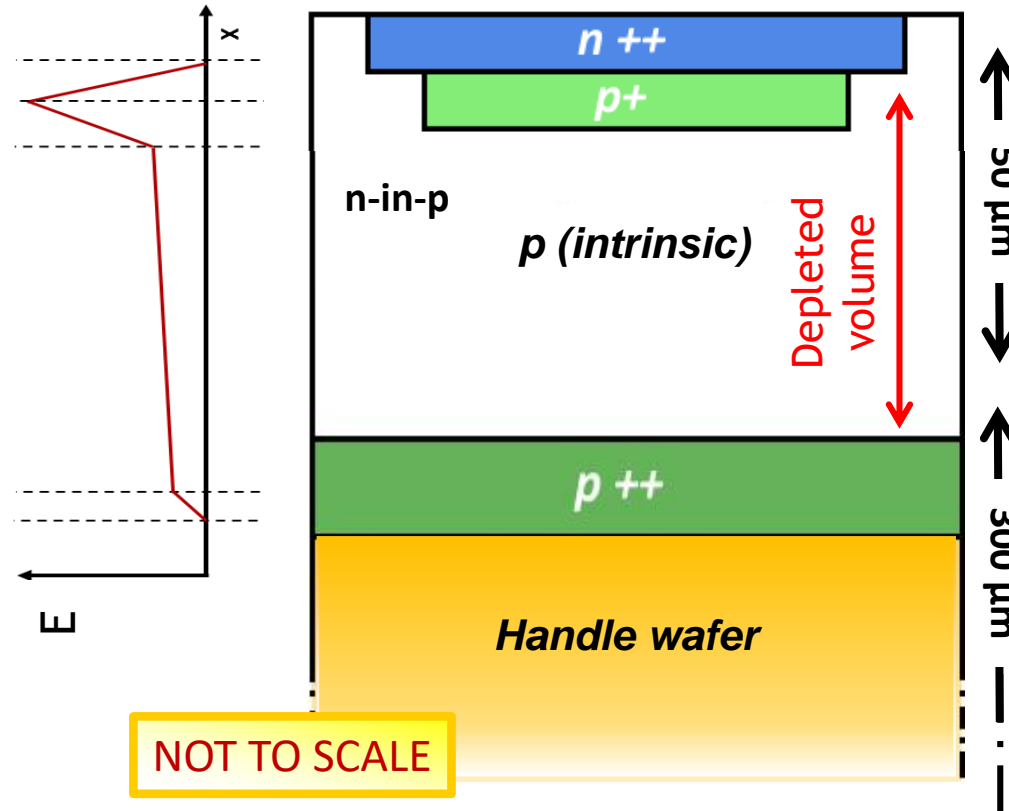
Small signal duration  
Good time resolution  
Radiation resistance

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Pile-up effects.

# Ultra Fast Silicon Detectors (UFSD)

$E \sim 300 \text{ kV/cm}$   
 $e^-/h$  avalanche multiplication



Thin  $p^+$  **gain layer** implanted under the  $n^{++}$  cathode;

small detector thickness;

controlled low gain ( $\sim 10$ ), increasing with reverse bias.

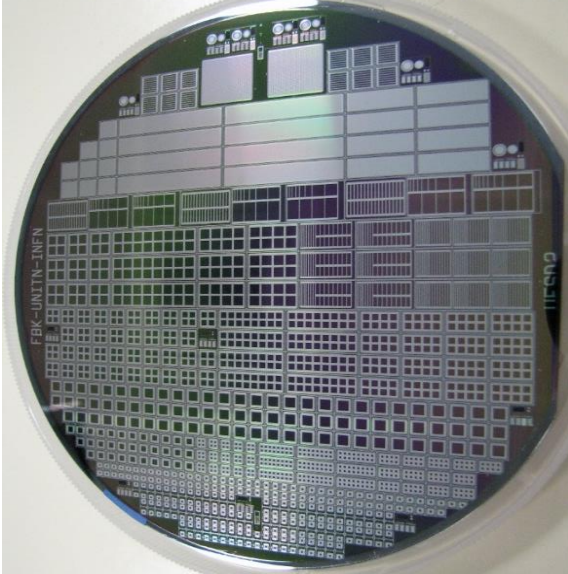
*H.F. W. Sadrozinski et al. Ultra-fast silicon detectors (UFSD) Nucl.Instrum. Meth. A831 (2016) 18-23.*

*V. Sola et al. Ultra-Fast Silicon Detectors for 4D tracking. Journal of Instrumentation (2017), Volume 12.*

**fast signal collection ( $\sim \text{ns}$ ) and excellent time resolution with S/N ratio of conventional Si detectors.**



# Production of 50 $\mu\text{m}$ UFSD prototypes @



18 silicon-on-silicon wafers

different **doping strategies**  
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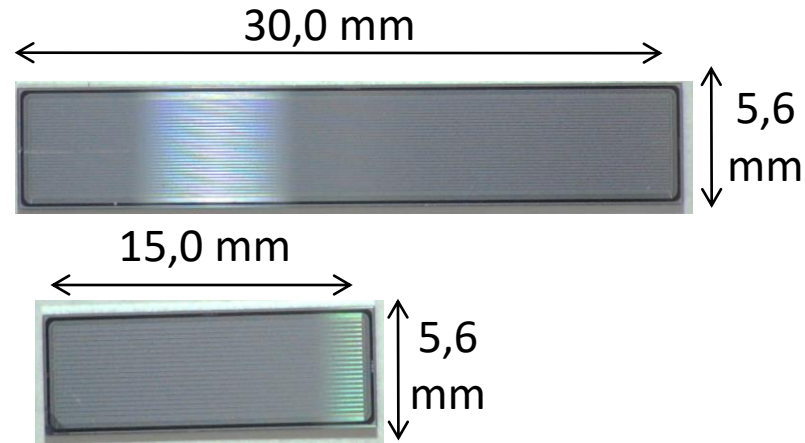


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30 strips, pitch 150  $\mu\text{m}$   
8 per wafer (2 no gain)

20 strips, pitch 200  $\mu\text{m}$   
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Same strip area, same  
capacitance  $C \sim 5\text{pF}$ ;

Gain and no-gain;

Total  $\sim 250$  structures.

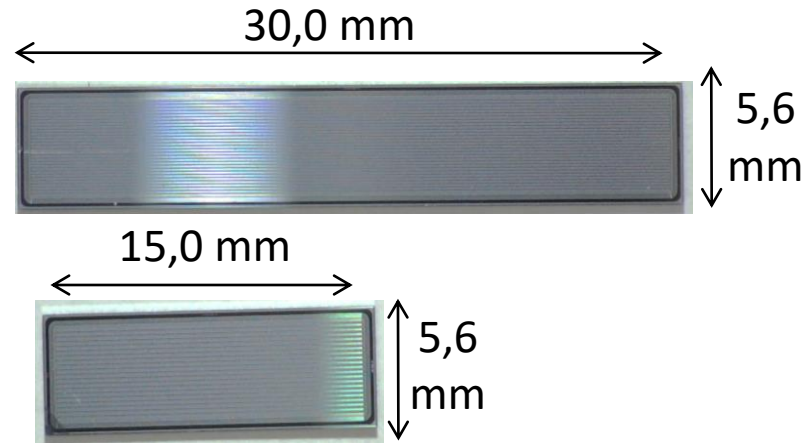
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Laboratory measurements (probe station + power analyzer and laser beam).

- **IV Curves** (Leakage current, breakdown voltage, bad strips)
- **CV curves** (Depletion voltage & doping profile of the sensor)
- **Laser tests** (dead area between strips)

# Beam tests of on a clinical beam (CNAO - Pavia)

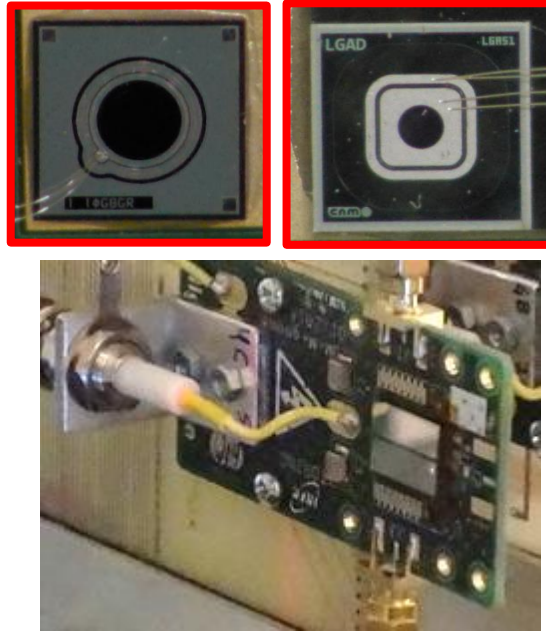
## Detectors

### 2 UFSD pads 50 $\mu\text{m}$ thick

- CNM 1,2 x 1,2  $\text{mm}^2$
- Hamamatsu (HPK)  $\varnothing$  1 mm

### MoveIT strip prototypes (FBK)

- Long and short geometries
- Only 2 ch. (1 gain + 1 no gain)



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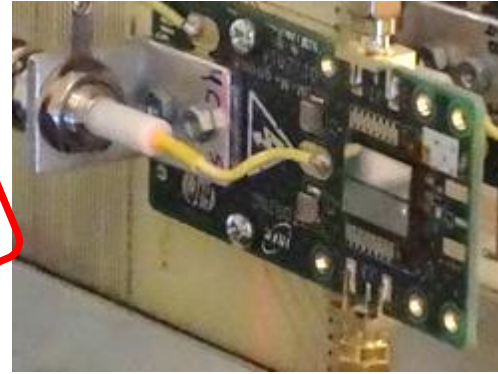
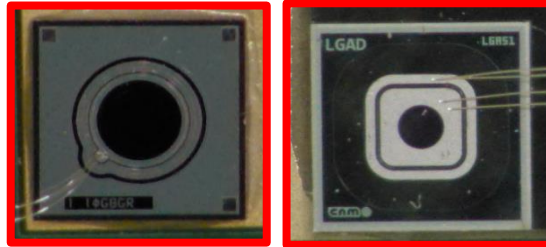
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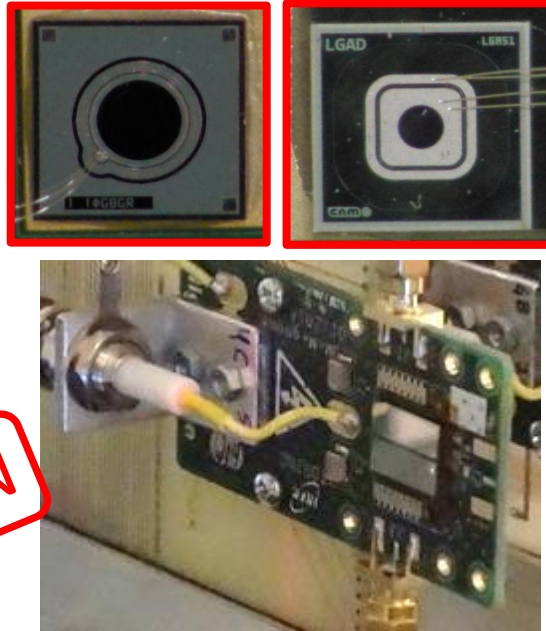
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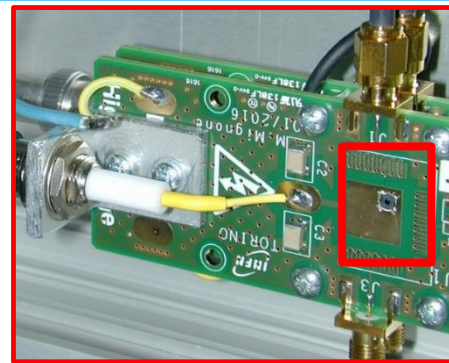
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- Passive FE boards aligned to the beam
- CIVIDEC broadband 40 dB amplifiers
- CAEN digitizer (5 Gs/s)



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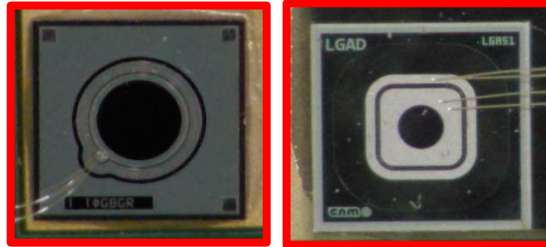
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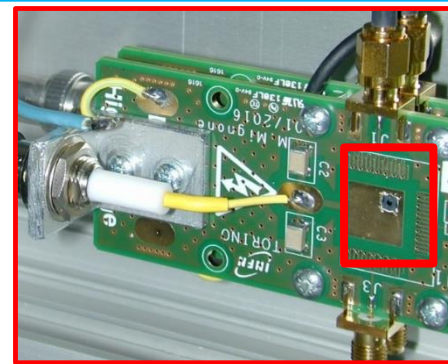
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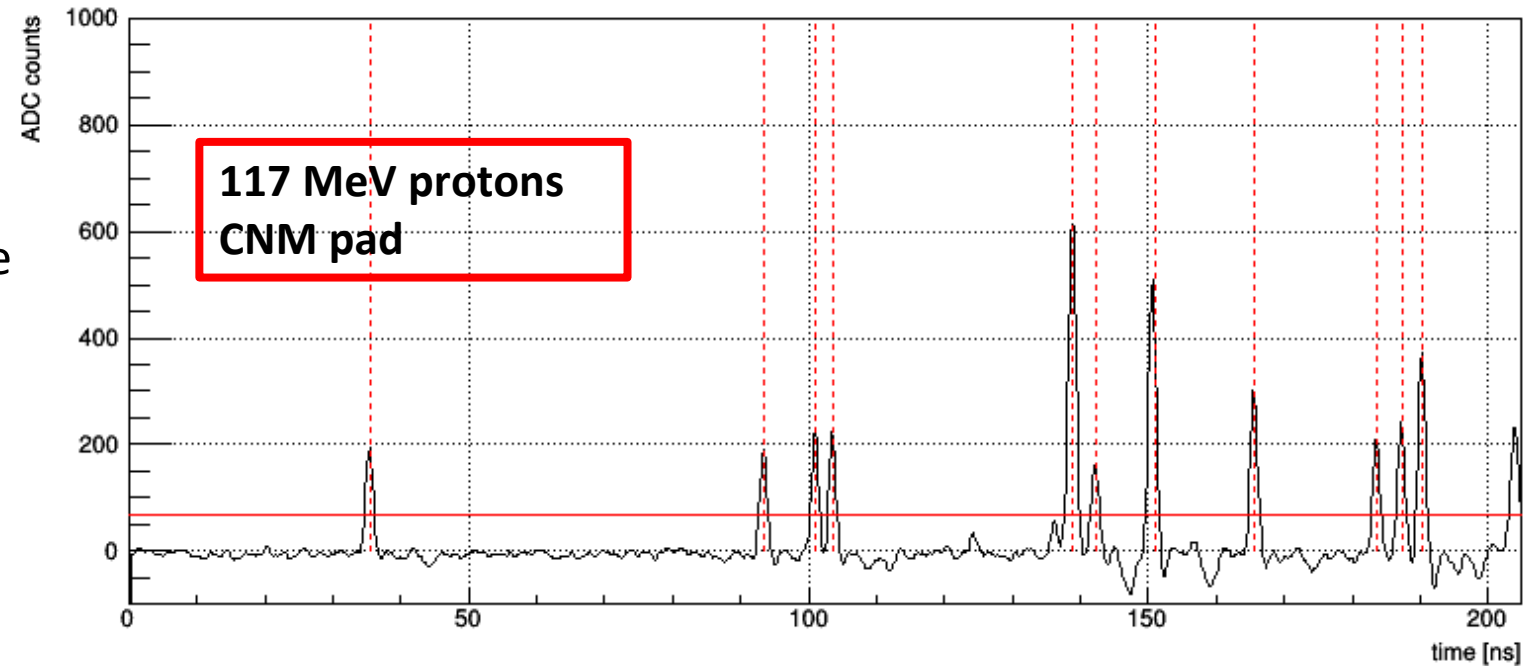


## CNAO Beam

- Clinical proton beam
- **Beam FWHM**  $\sim$  10mm
- **Max flux**  $\sim$  10<sup>9</sup> p/s delivered in spills ( $\sim$  1s duration)
- **Beam flux** range:  
20% - 100% of max flux.
- **Beam energy** range:  
62 – 227 MeV (5 – 2 MIP)

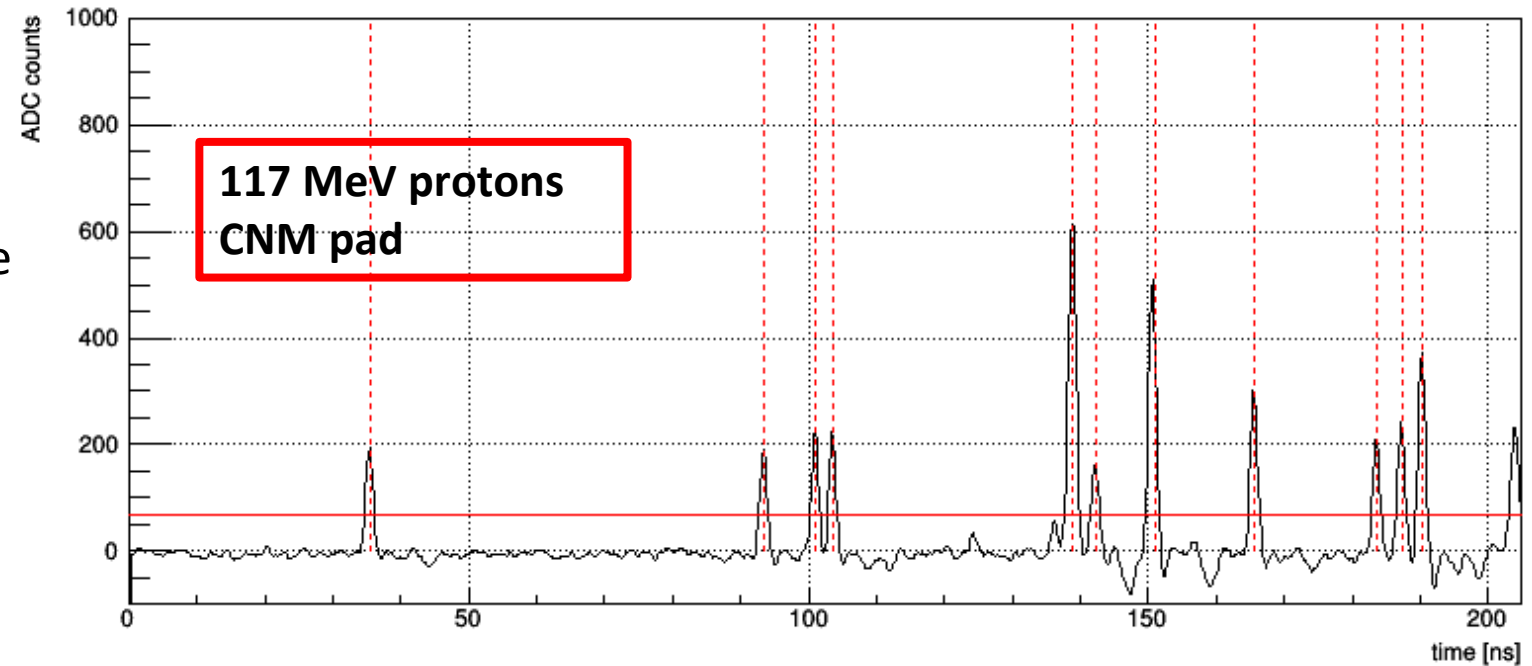
# Signal waveform acquired on the CNAO beam

- ✓ CNM pad (1,4 mm<sup>2</sup>)  
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- ✓ average beam fluence rate  
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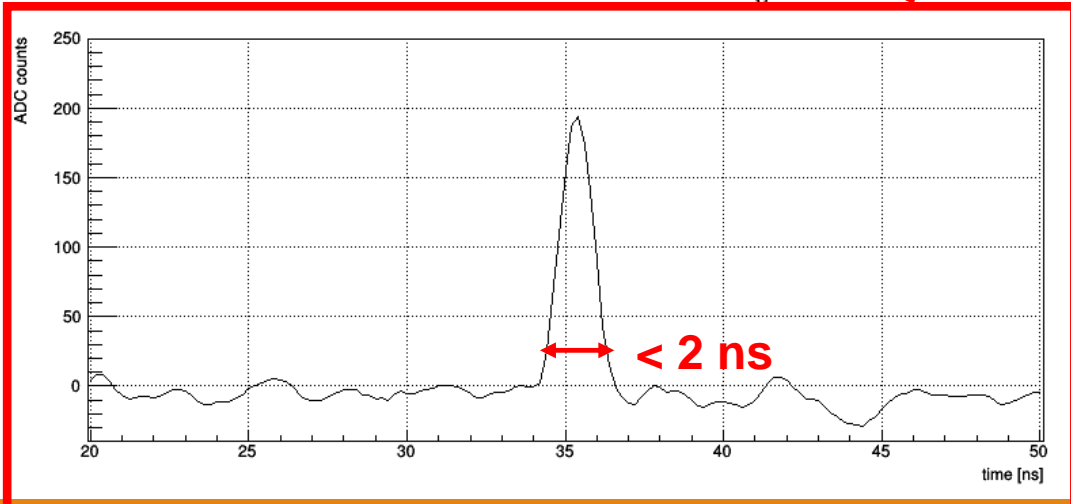
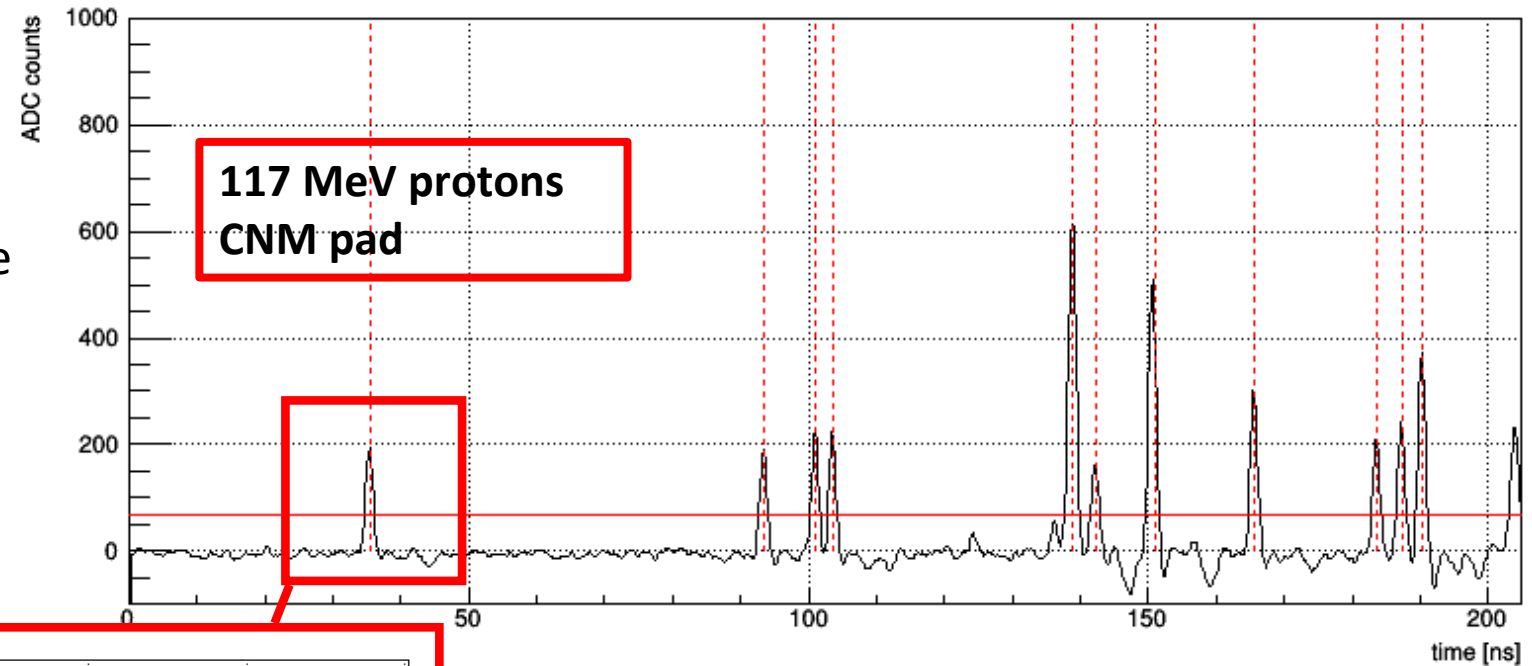


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- large amplitude fluctuations;



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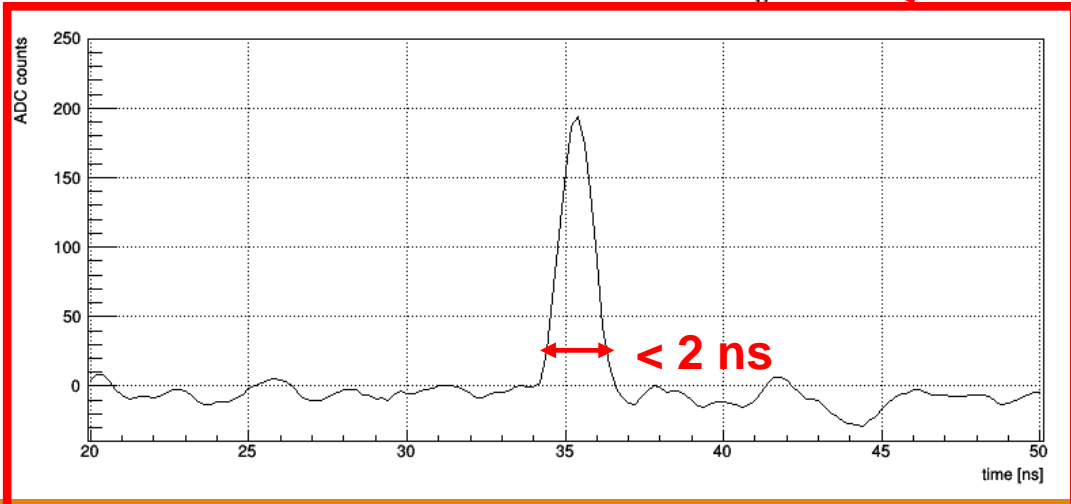
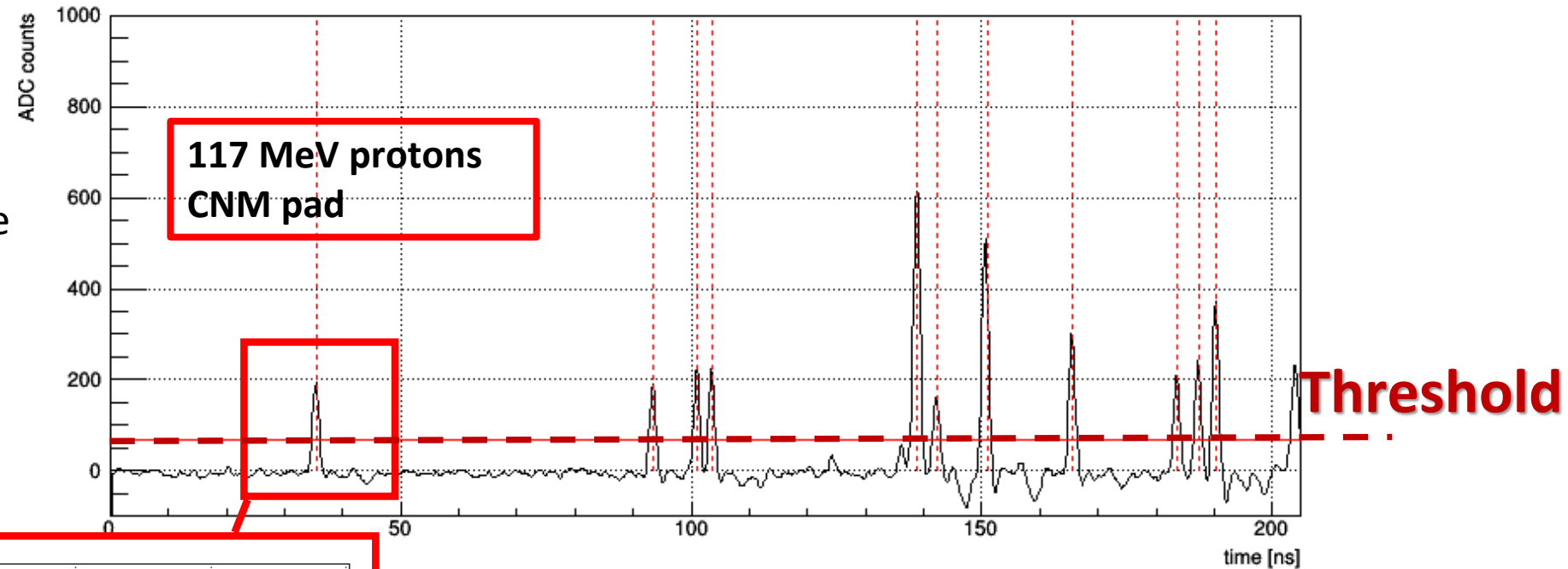
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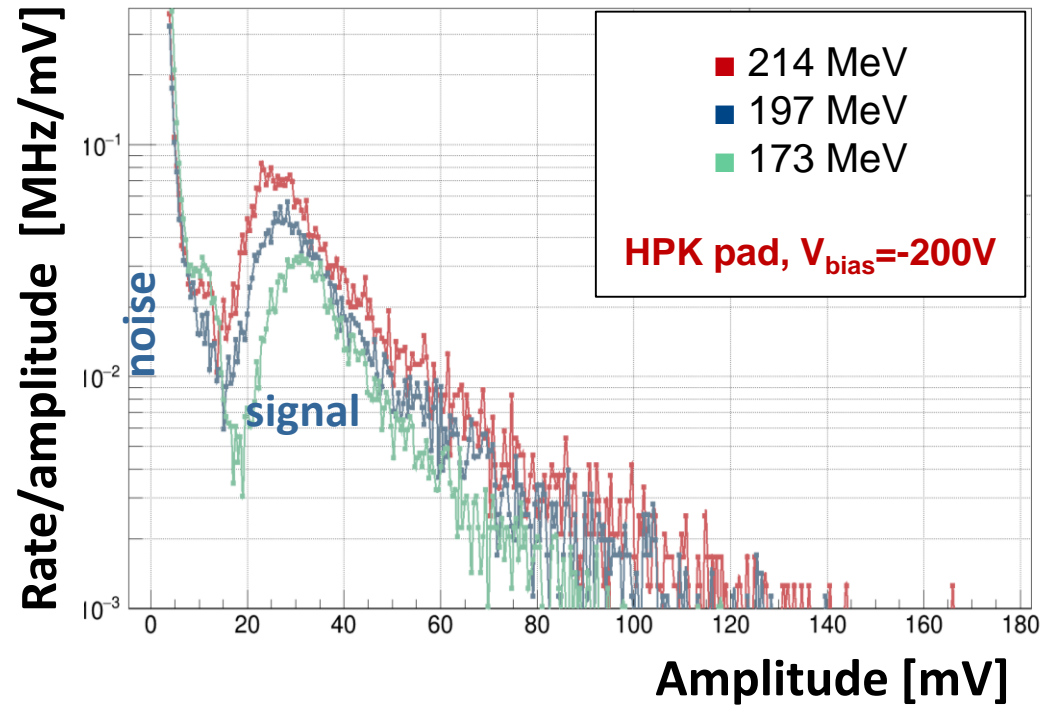
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- short peak duration;
- fixed threshold can be applied to count the pulses.

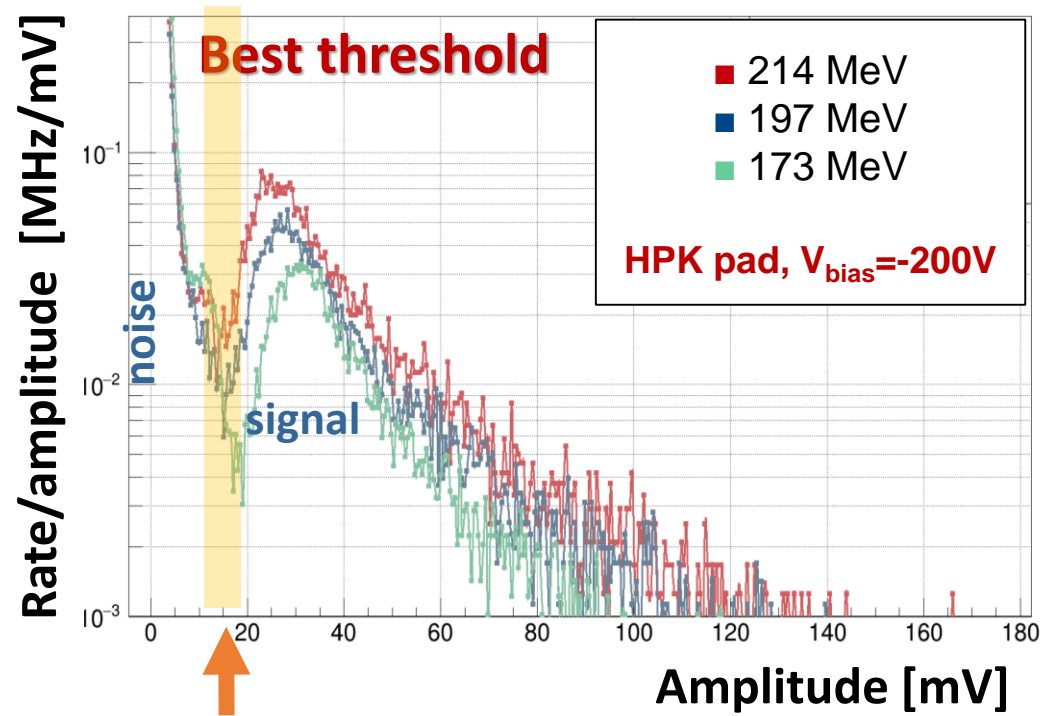
# Signal & noise distribution

## Signal amplitude distribution



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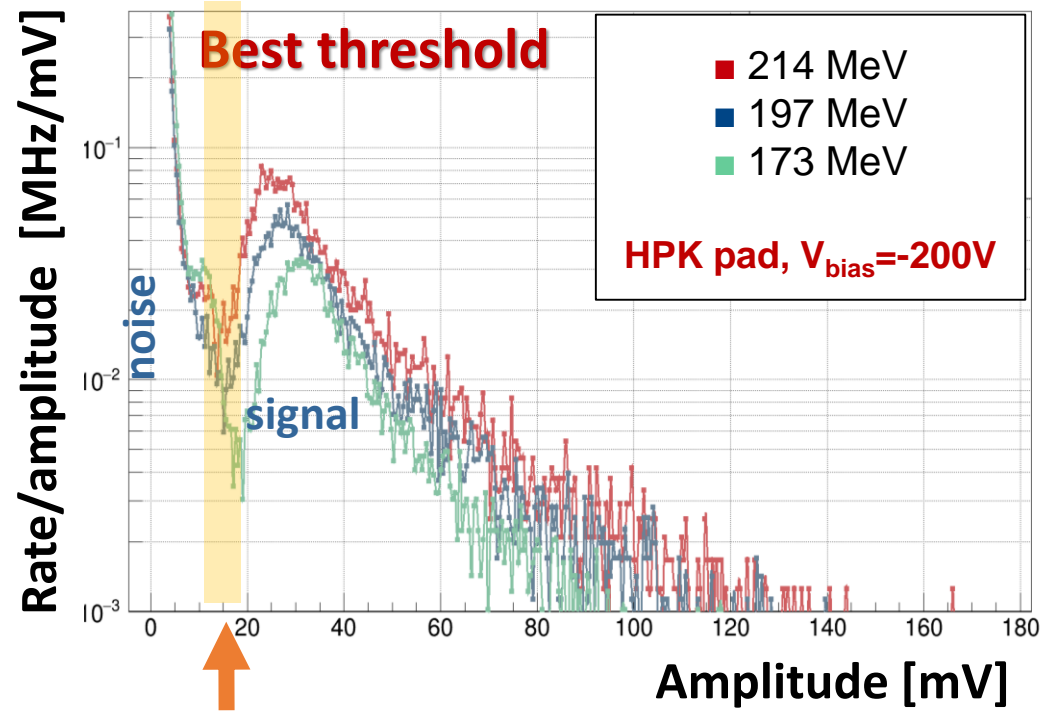
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- Good S/N separation;
- Larger S/N at lower beam energies;
- Best threshold is beam energy dependent.

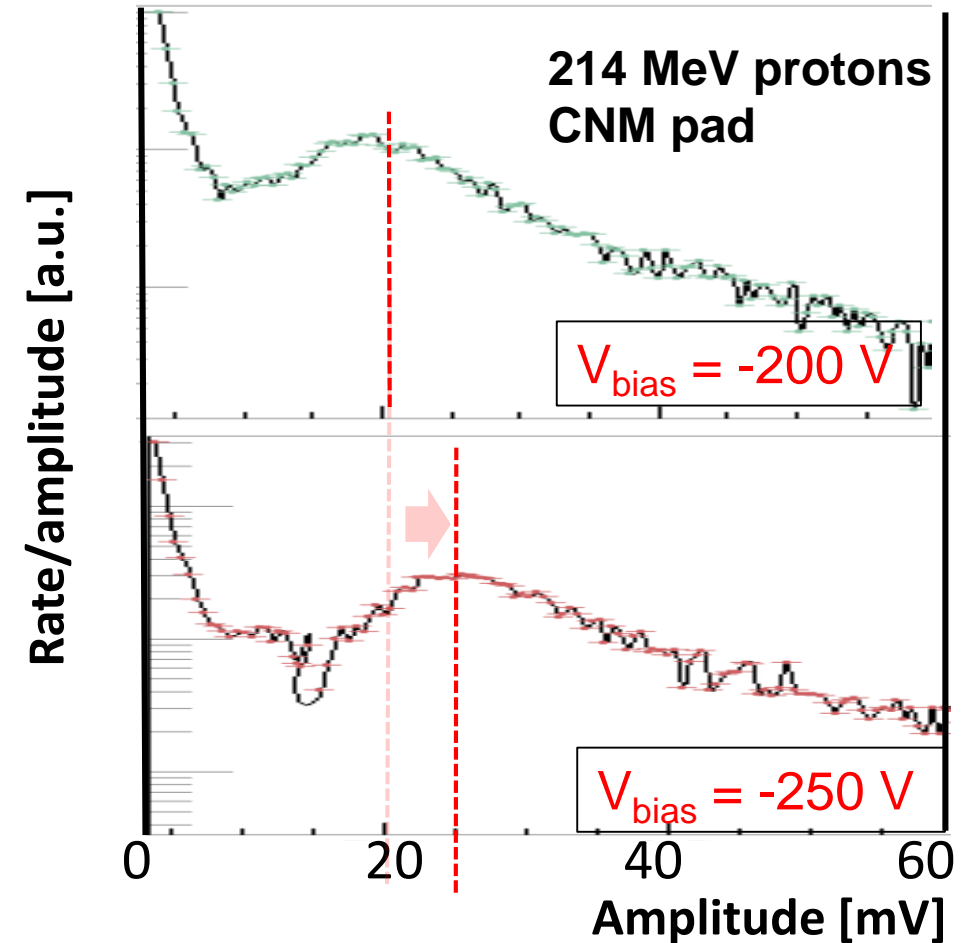
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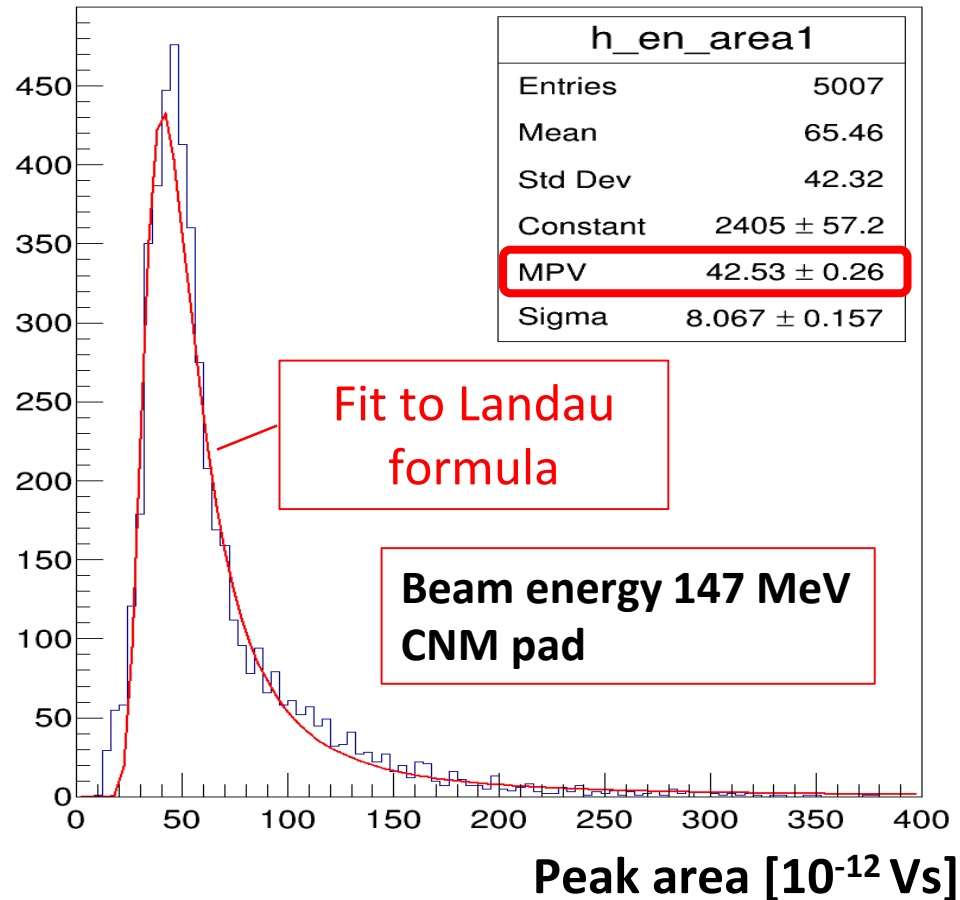
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The S/N can be enhanced by increasing the bias voltage → gain increase in the sensor



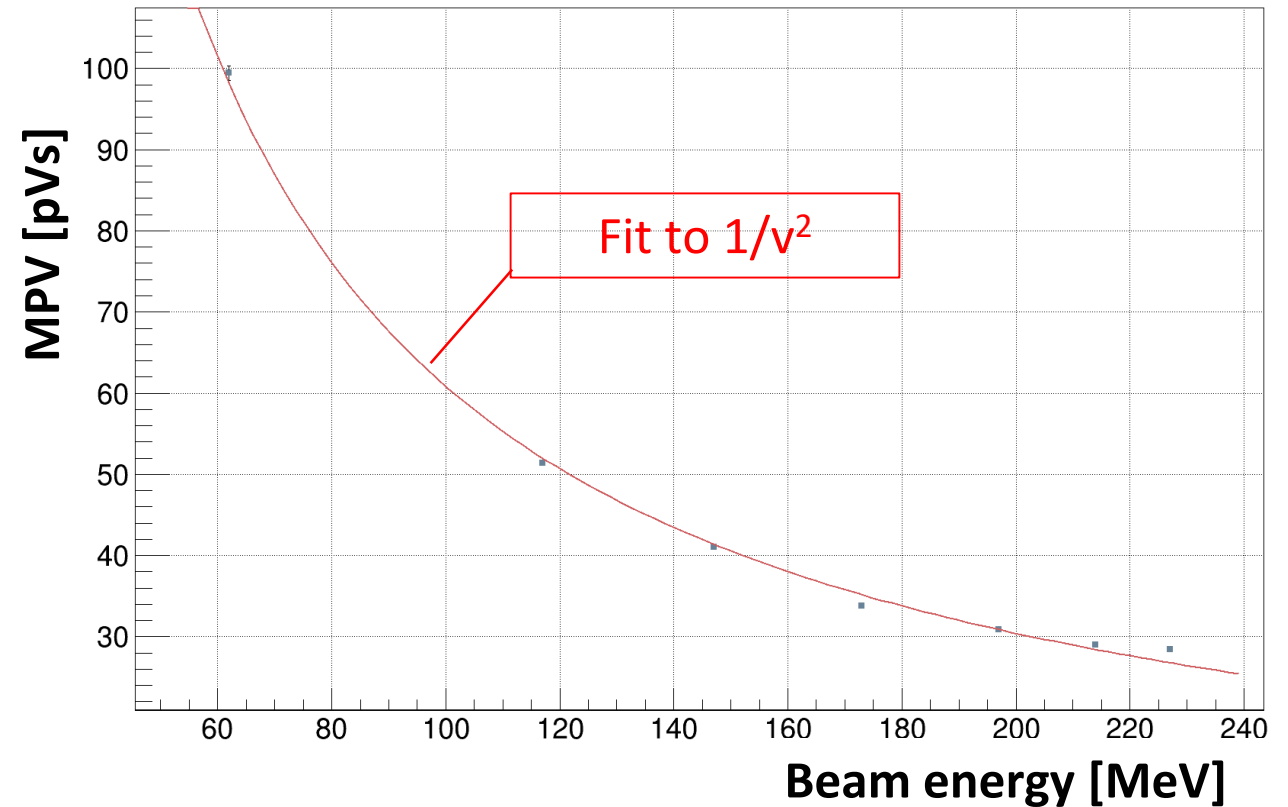
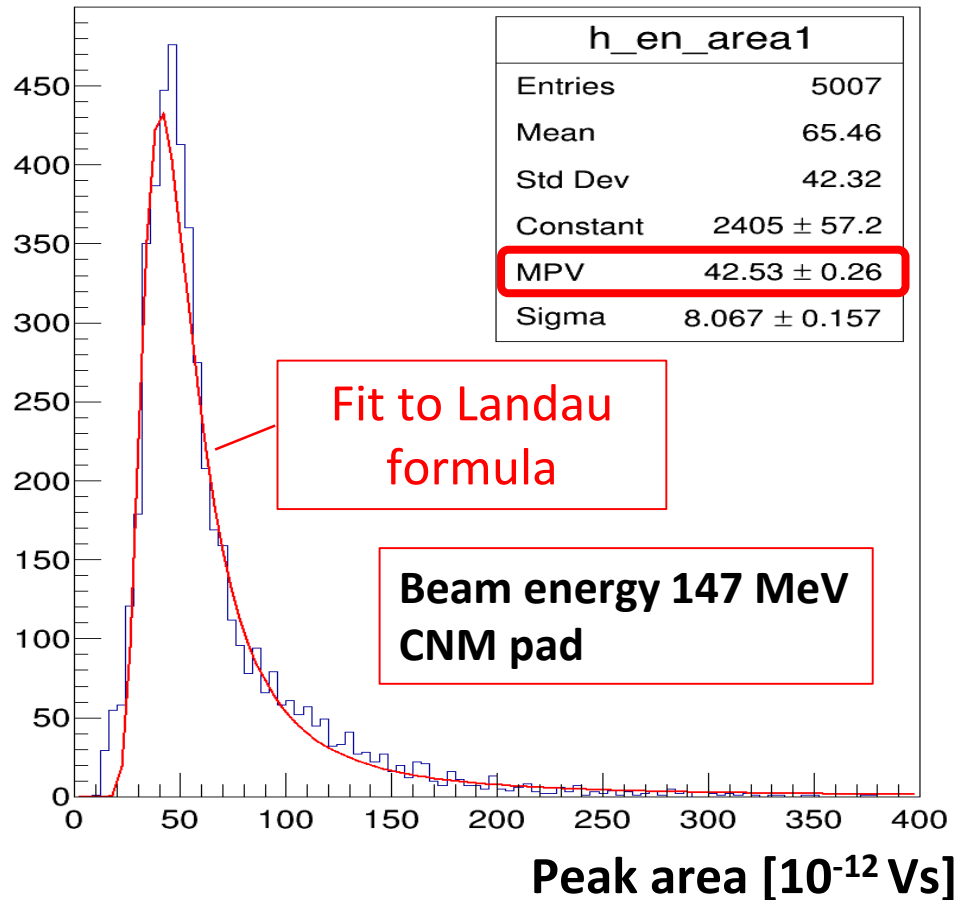
# Peak area & Landau distributions

- Area of peaks proportional to collected charge;
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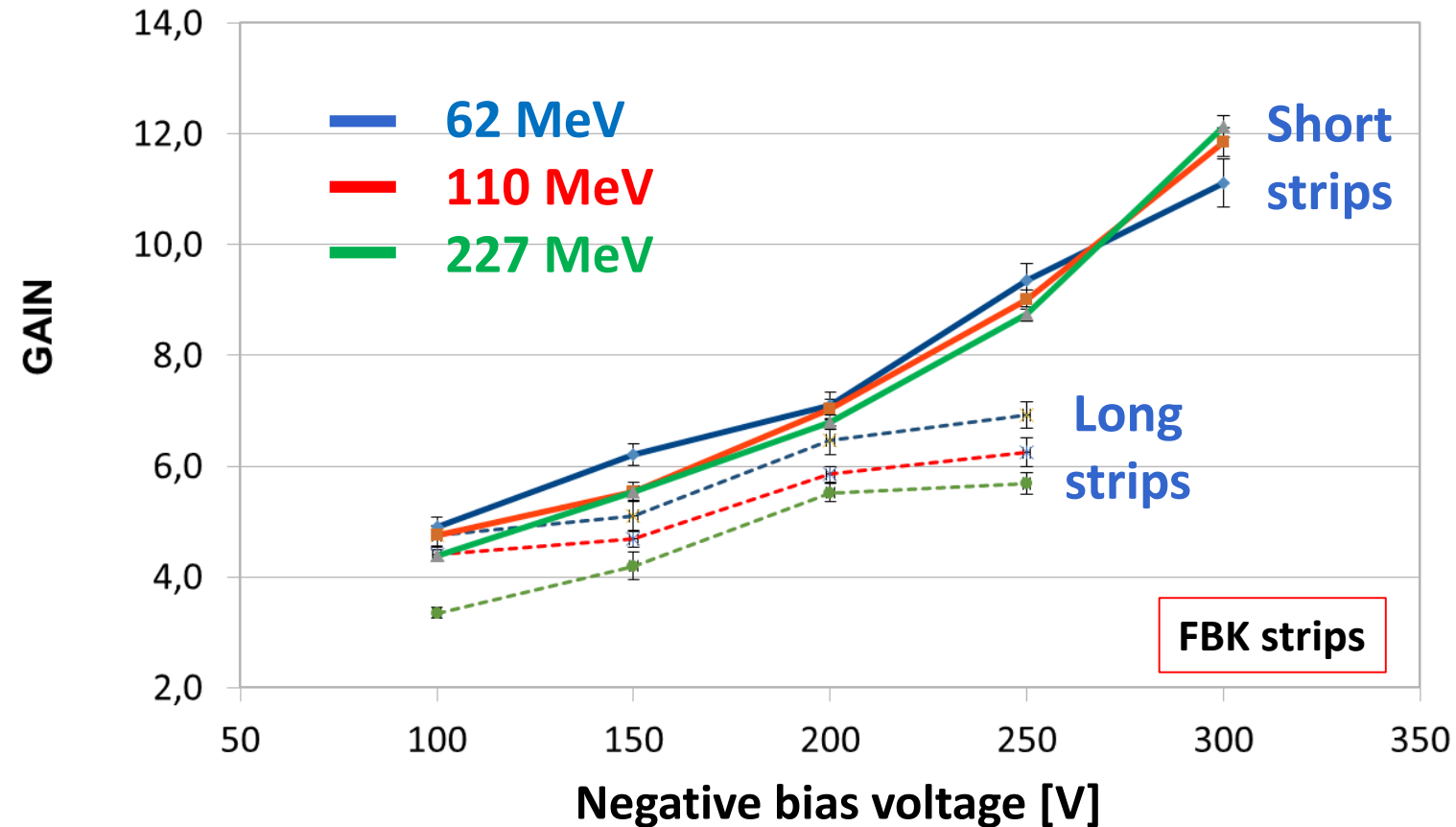
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- Landau's MPV dependence on **beam energy** well described by Bethe-Bloch  $1/v^2$  dependence



# Gain of strip detectors

$$\text{Gain(V)} = \frac{\text{MPV}_{\text{gain}} \text{ (V)}}{\text{MPV}_{\text{no gain}} \text{ (V)}}$$

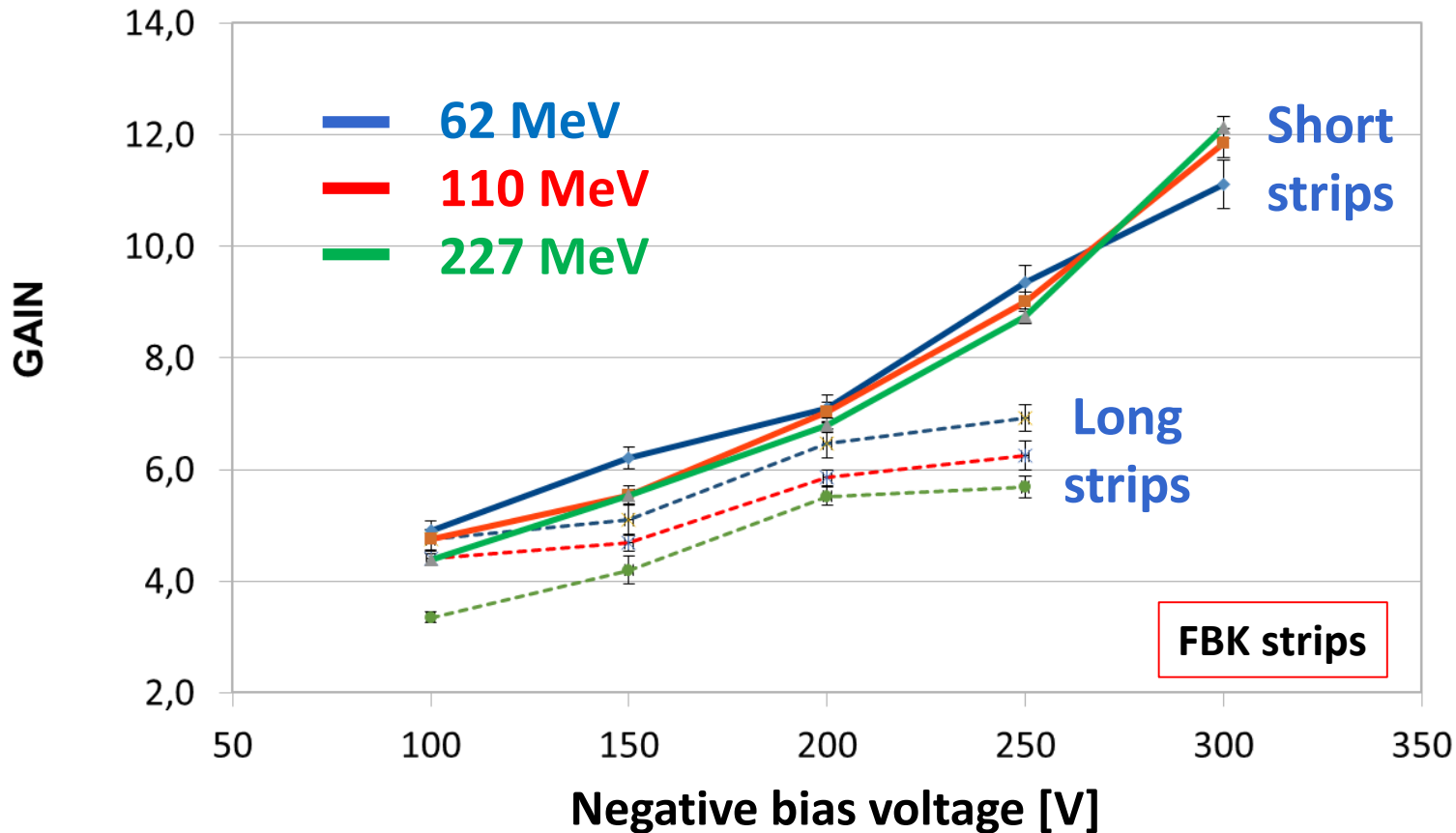
➤ Gain increase with  $V_{\text{bias}}$





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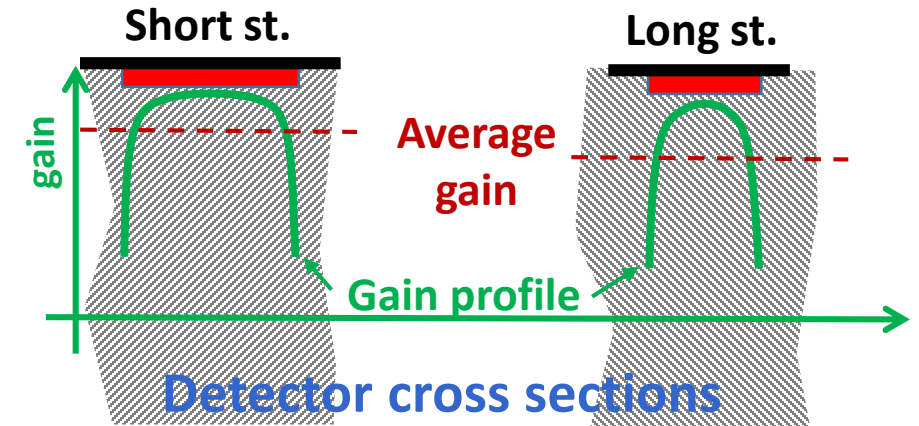
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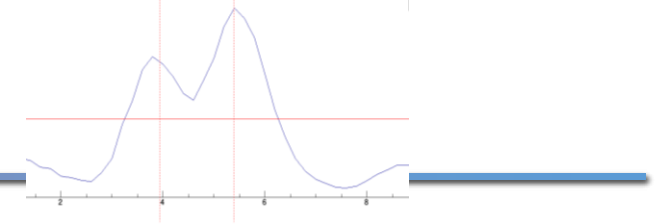
➤ Gain increase with  $V_{\text{bias}}$

➤ **Long strips** (thinner) show a **lower average gain** than short strips

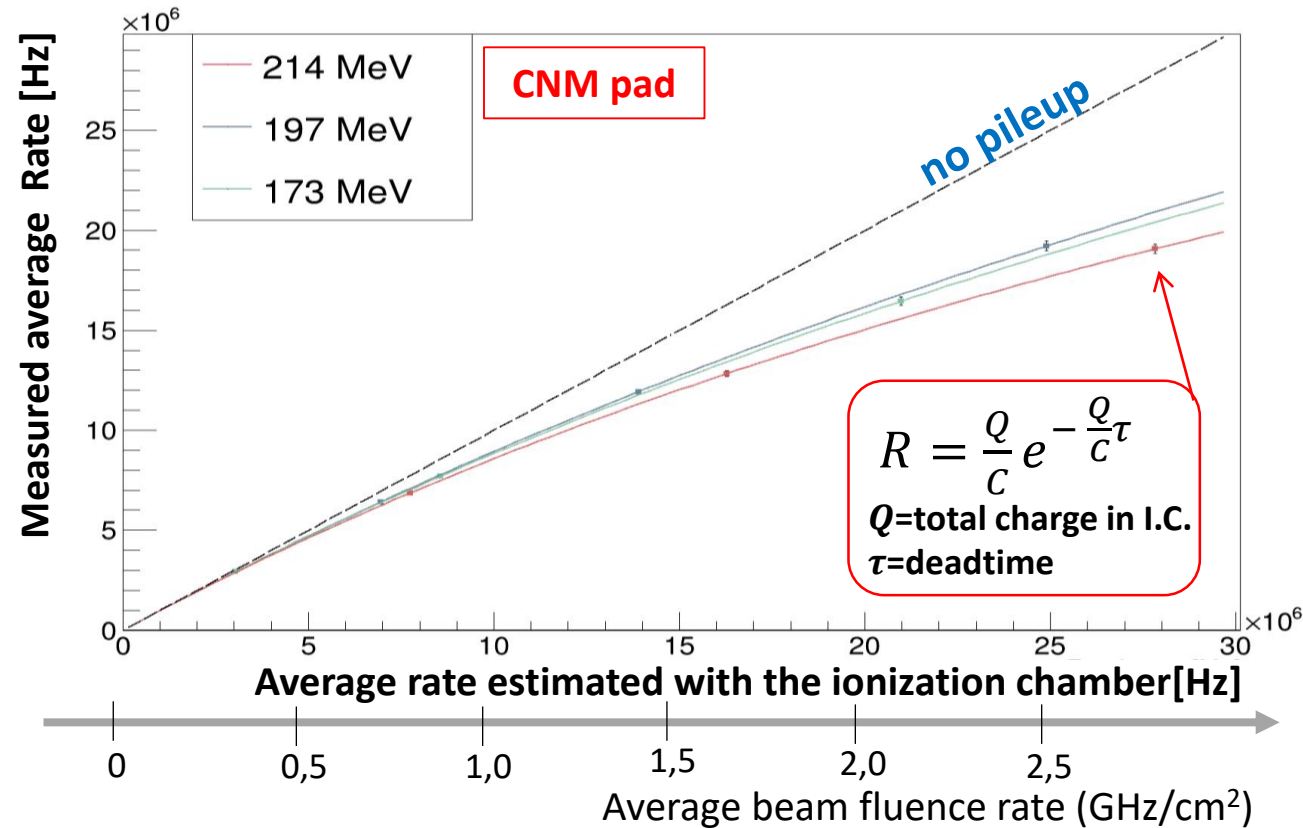
➔ geometrical effect



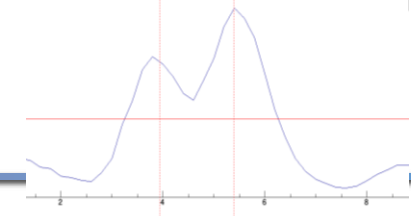
# Concern: pile-up inefficiency



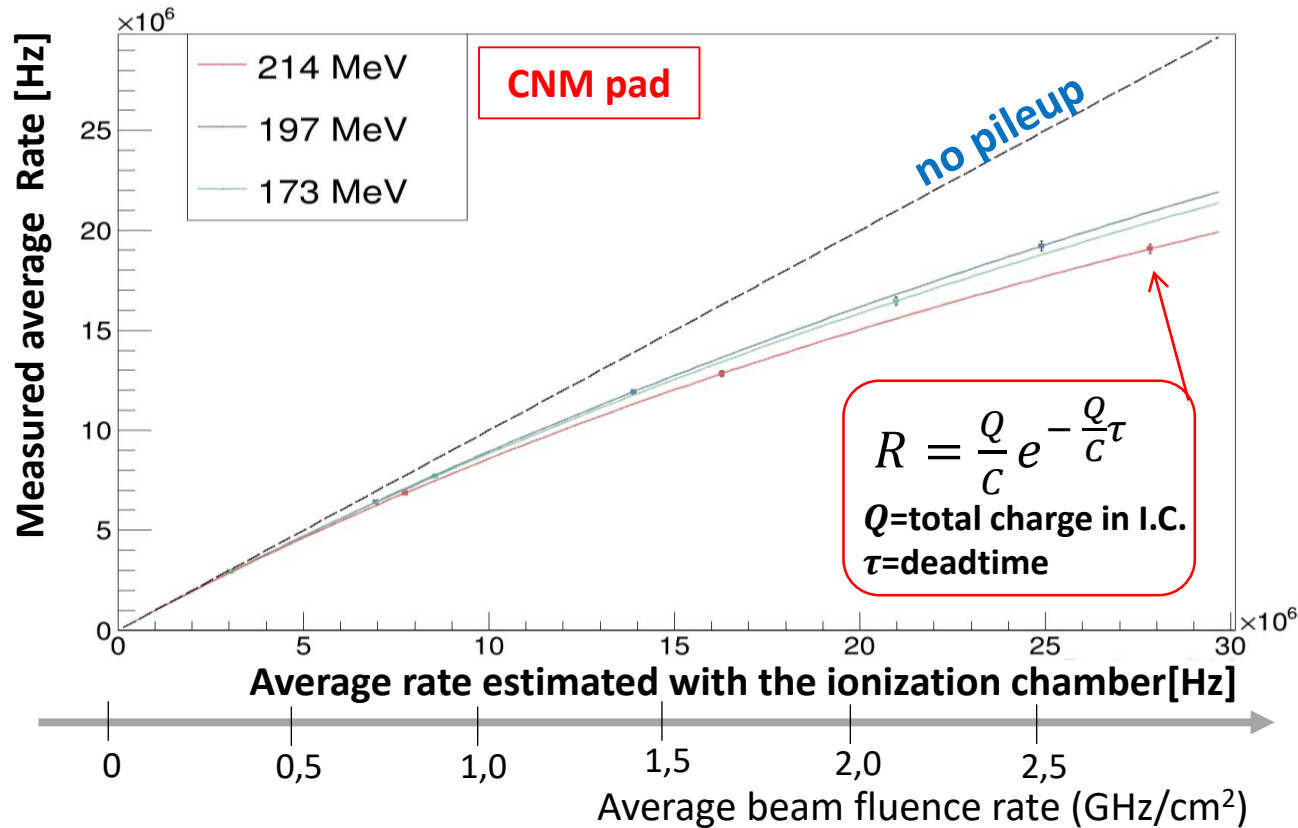
**Measured vs. estimated rate**, using a PTW pinpoint I.C. and a varied beam flux (20 – 50 – 100% of max)



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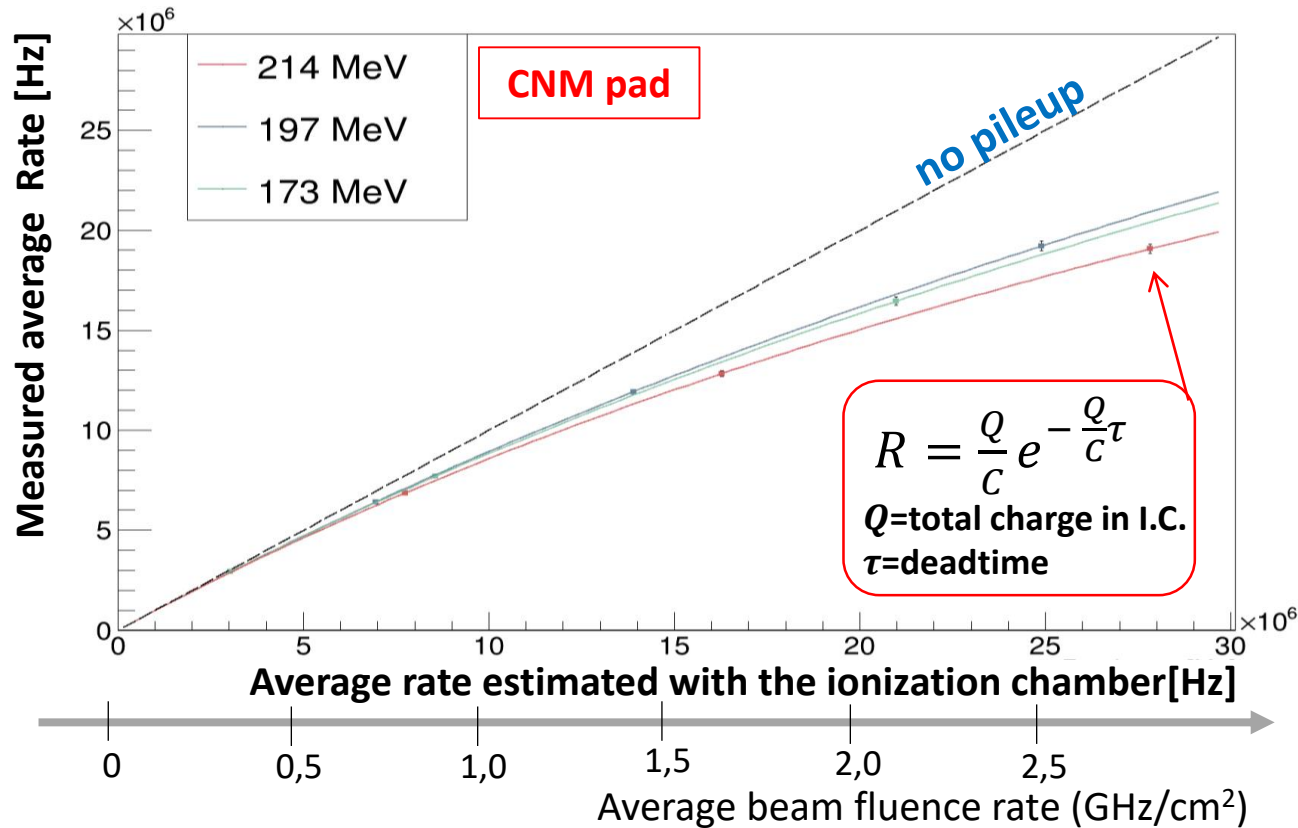
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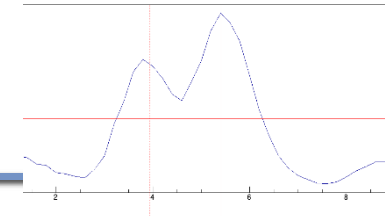
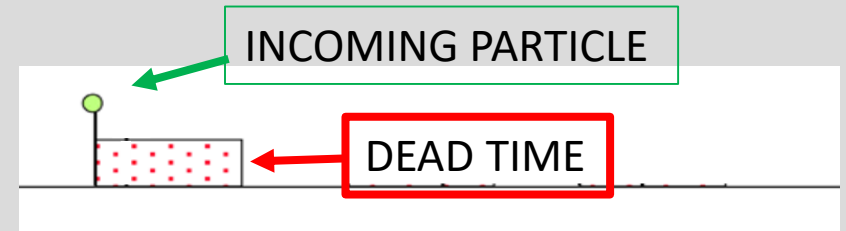
- Large inefficiency observed (up to 25% at largest clinical fluxes) ➡ Correction required
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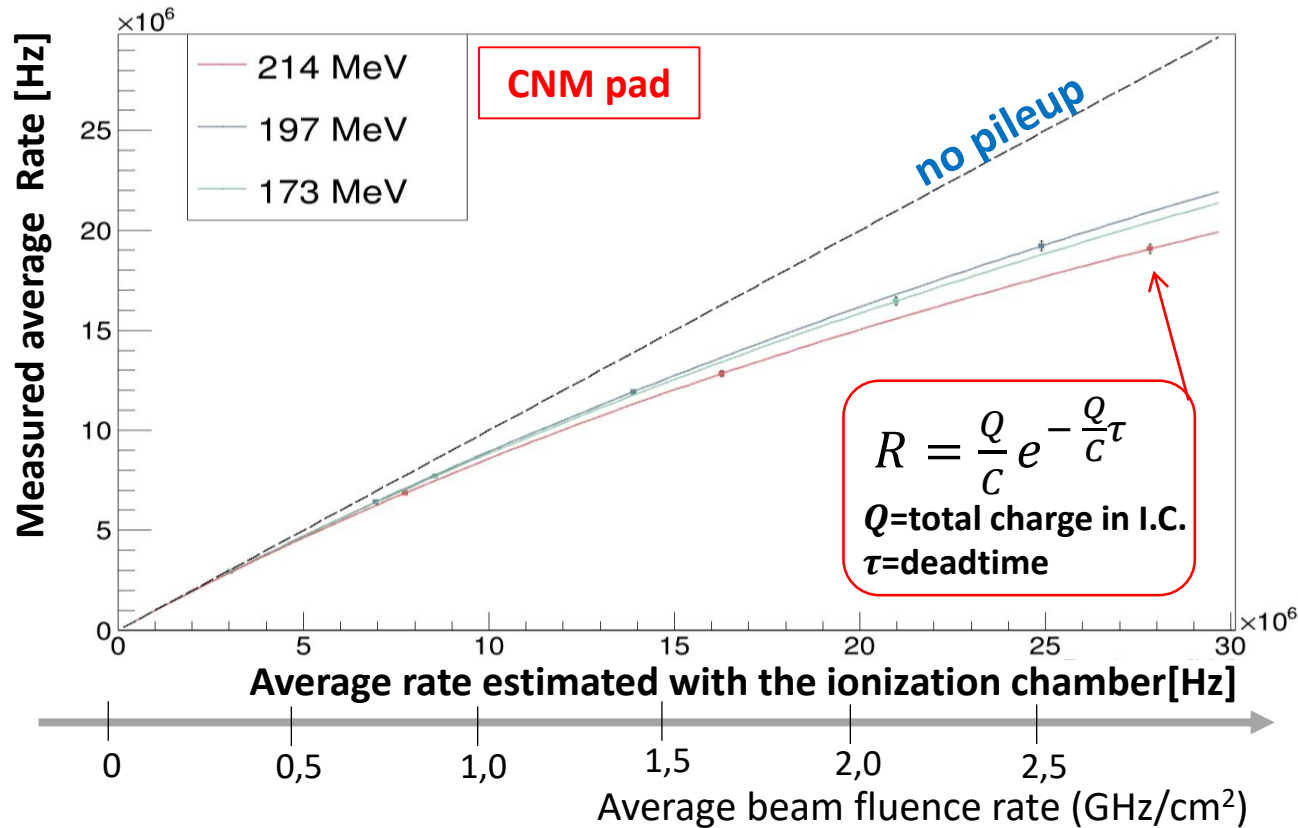


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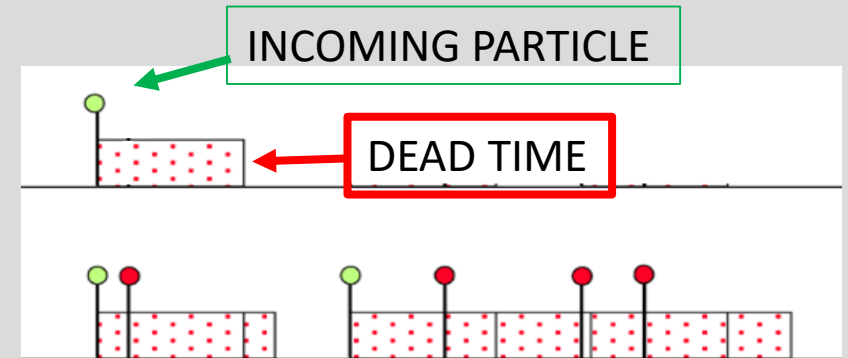


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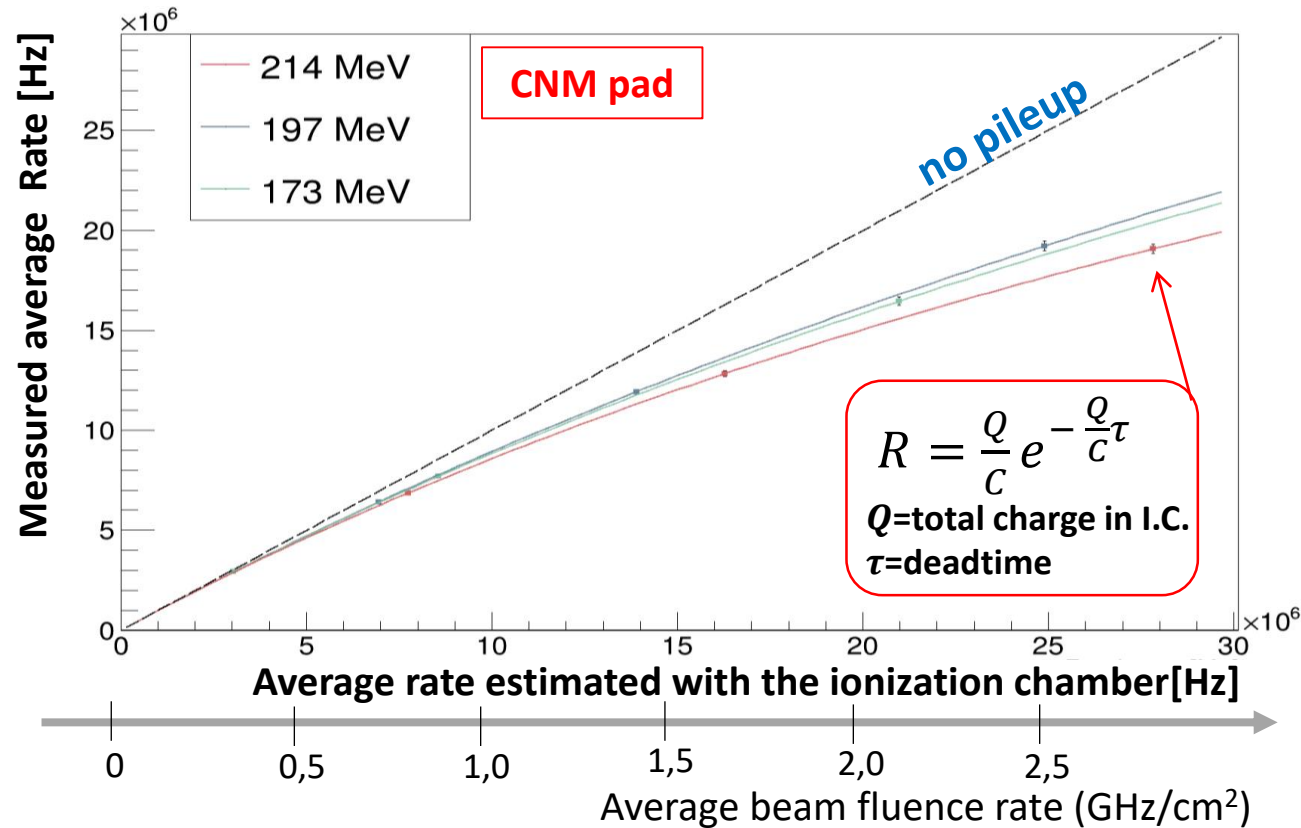


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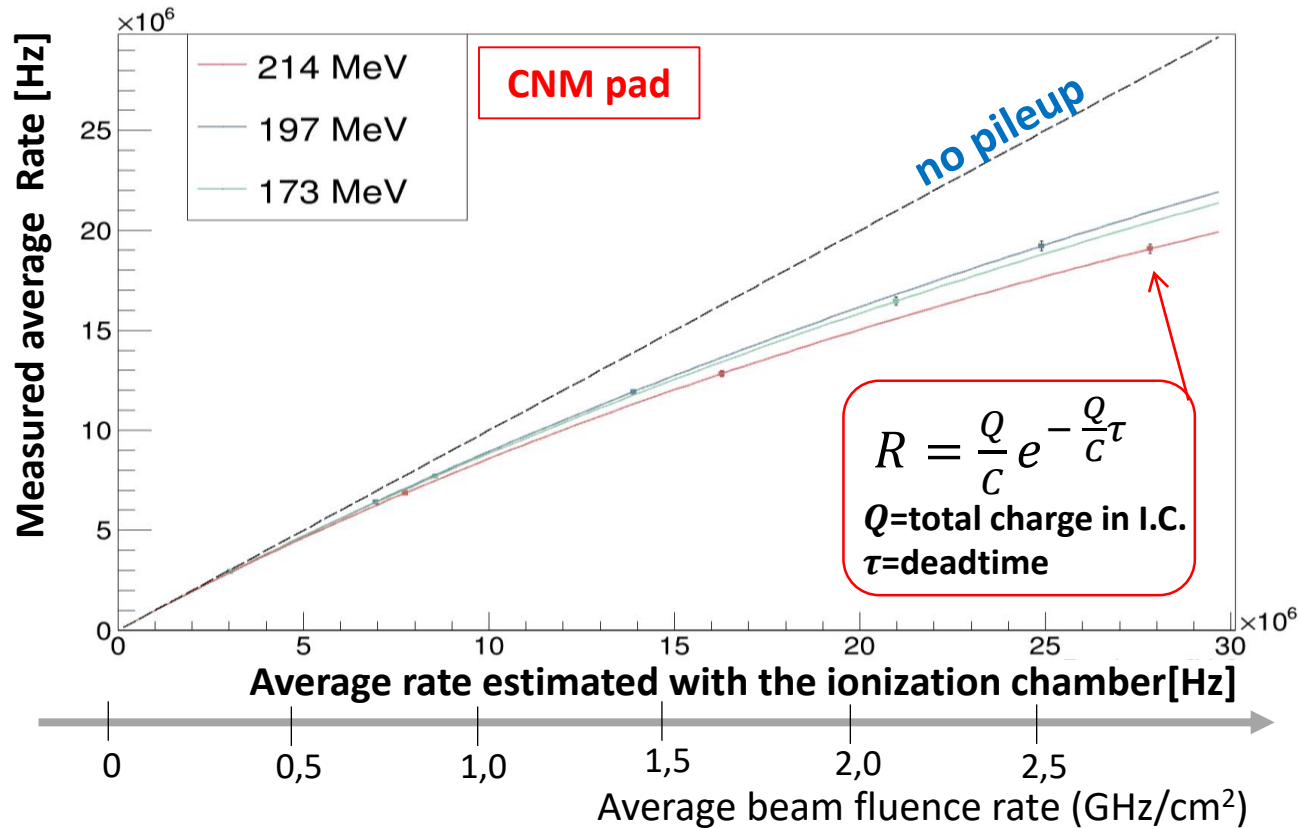
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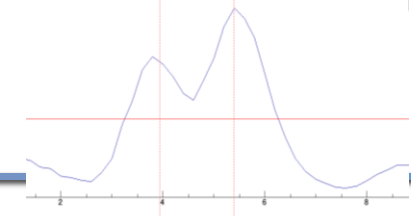
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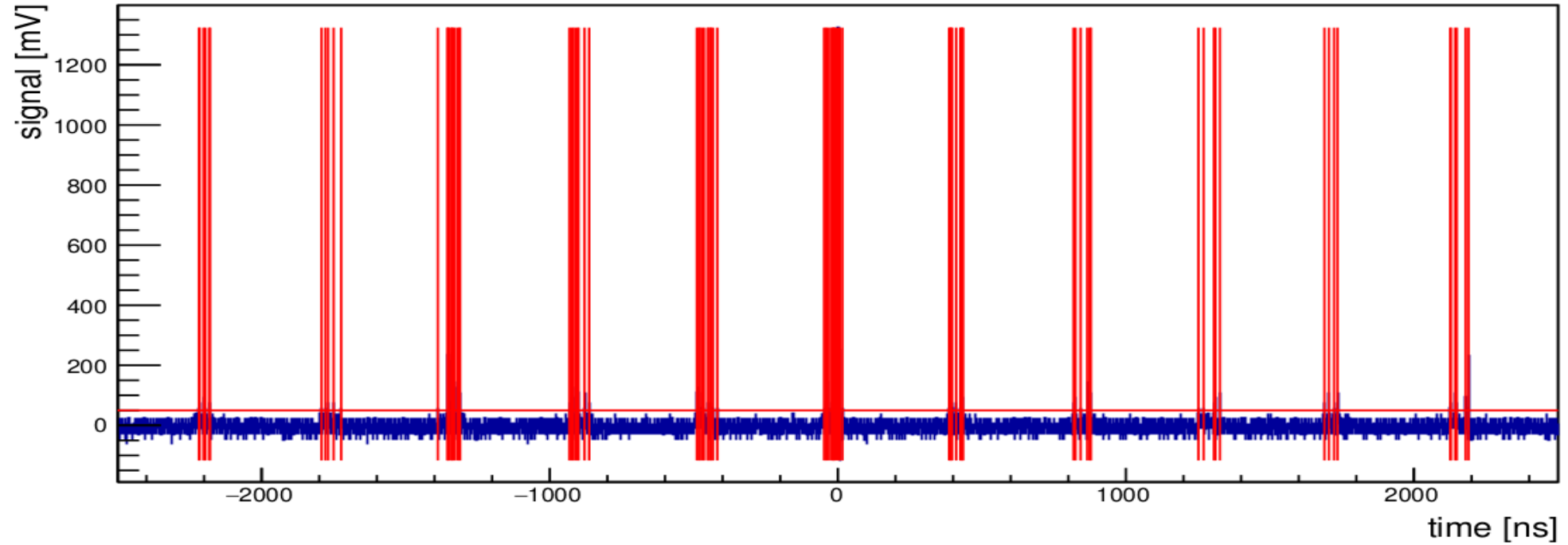
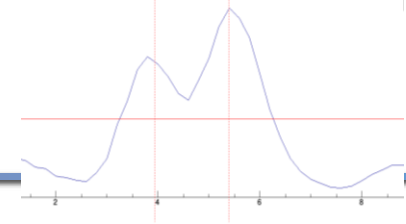
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- Large inefficiency observed (up to 25% at largest clinical fluxes) ➡ Correction required
- Data well described by paralyzable pileup model ➡ deadtime **much larger than expected**
- Reason relies on the bunched structure of the CNAO beam (instantaneous flux  $\sim 10 \times$  average)

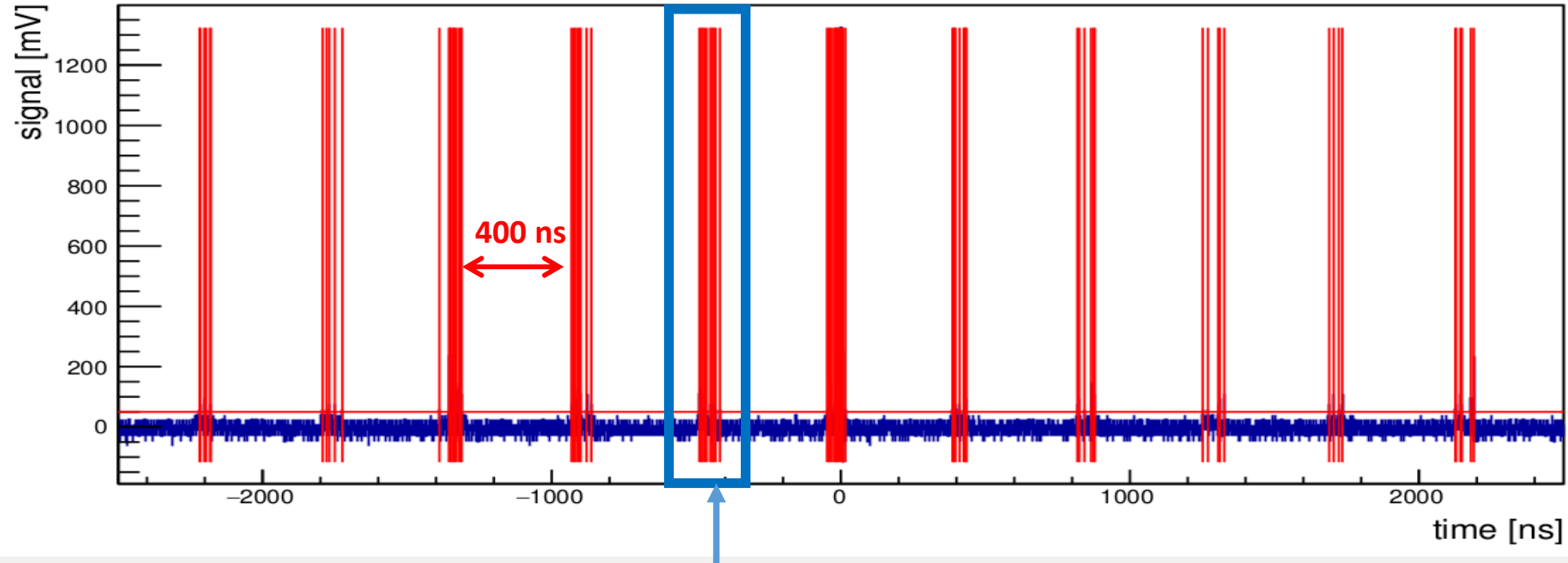
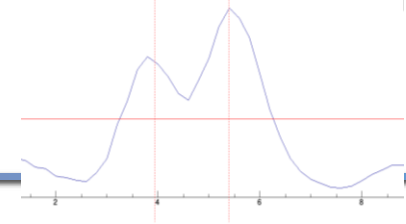


# Concern: pile-up inefficiency





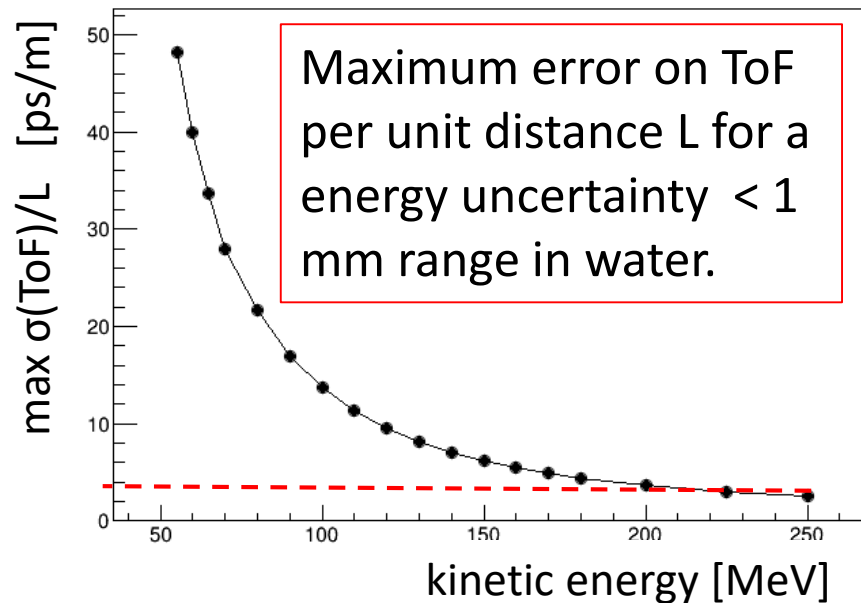
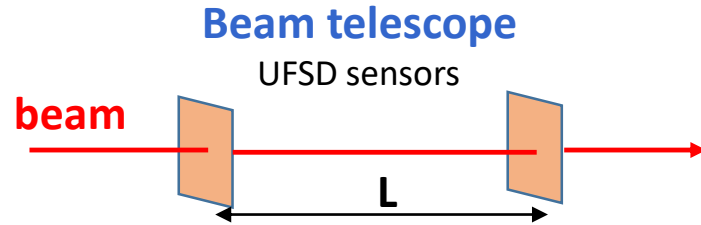
# Concern: pile-up inefficiency



$\sim 10^{10}$  p/s  $\text{cm}^2$  !!



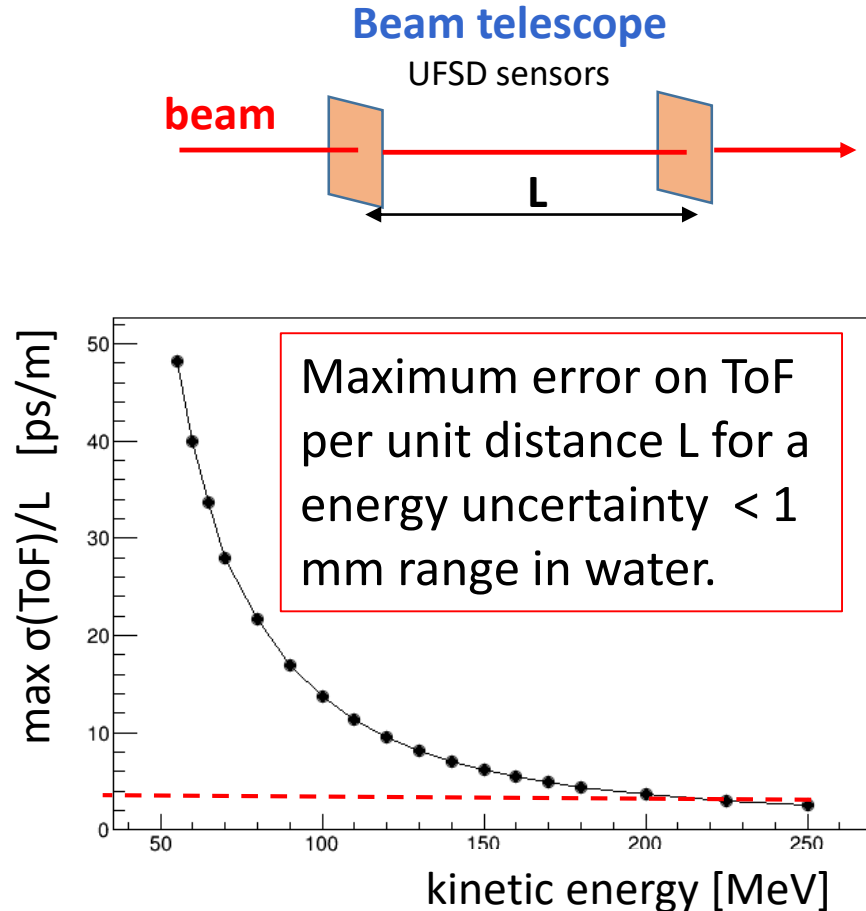
# Beam energy measured from Time-of-Flight



- For 1m distance the **max error on TOF < 4 ps**
- Large number of coincidences are needed



# Beam energy measured from Time-of-Flight



- For 1m distance the **max error on TOF  $< 4$  ps**
- Large number of coincidences are needed

## Time difference for pulses in coincidence in 2 pads

- Beam  $E = 114$  MeV, total acquisition time  $300 \mu\text{s}$  (less than average spot duration), CFD algorithm applied on pulses signals

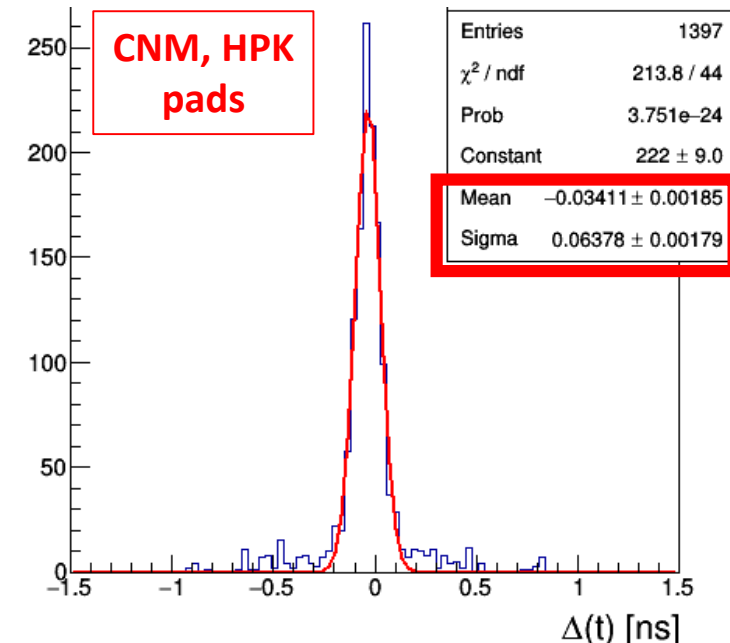
Stat error on  $\langle \text{ToF} \rangle$   
**2 ps**

## Time resolution of single hit

$$\sigma(t) = 64\text{ps}/\sqrt{2} = 43 \text{ ps}$$

## Remarks

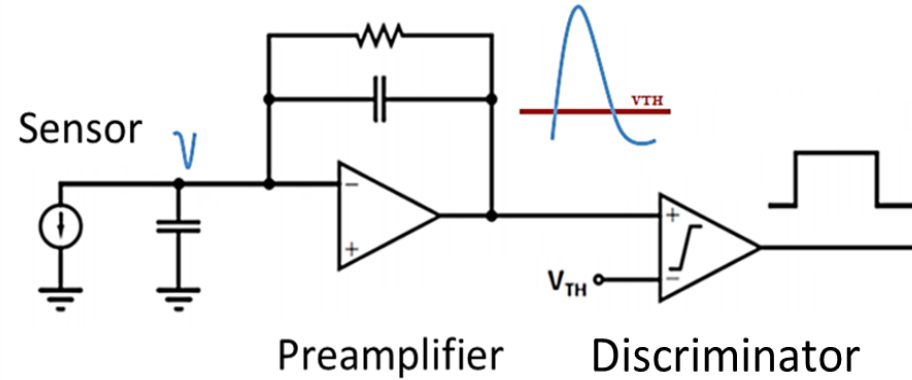
- Sensors at 2cm distance (favorable condition)
- Ongoing simulations for optimizing the geometry and the ToF reconstruction method



# Fast readout electronics (TERA10)

## Requirements

Input ch. range: **3 fC ÷ 140 fC**  
Rate/channel: **up to 200 MHz**  
Inefficiency **< 1 %**.

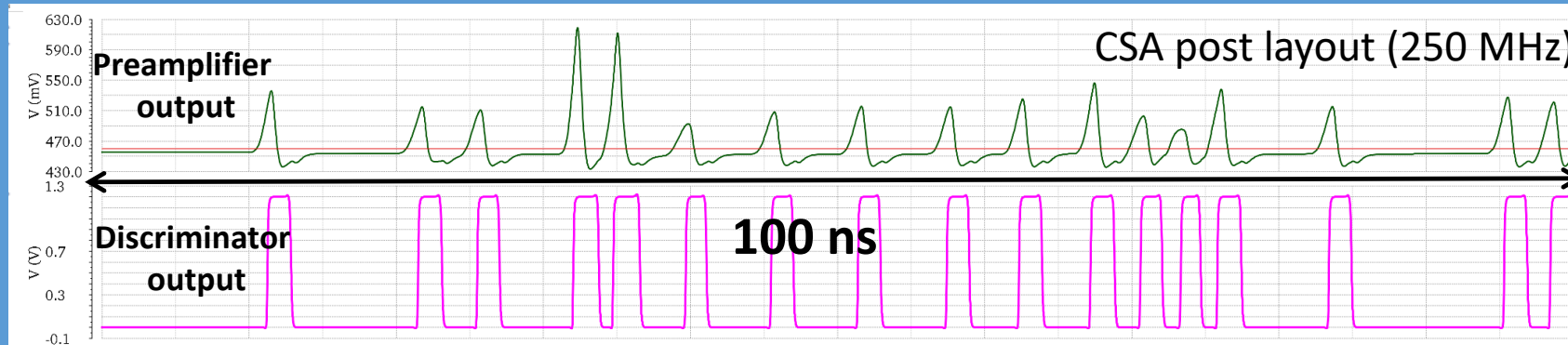


## FPGA

- FE initialization
- Pulse counting
- Pileup correction

+ Additional functionalities  
(threshold scan, ....)

2 alternative designs (CSA & TIA) of the amplifier developed and compared



**Prototypes (24 ch) of the 2 architectures submitted in UMC110 technology, available in April**

# Conclusions

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UFSD detectors are a promising new technology for beam qualification and monitoring in Particle Therapy

- Fast collection time + Large S/N ratio
  - ➔ directly count of number of ions of a clinical beam
- Excellent time resolution
  - ➔ measurement of the beam energy

# Open issues for clinical applications

## ➤ Radiation resistance:

- large effort in HL-LHC community for achieving resistance up to  $\Phi > 10^{15} \text{ n/cm}^2$
- Extensive radiation tolerance tests have been carried on with pads of the same USFD production of the strips:
  - gain can be recovered up to  $10^{15} \text{ n/cm}^2$  for some of the options tested;
  - protons worse than neutrons by factor 2.

## ➤ Pileup inefficiency

- Many correction methods are proposed in literature.
- Additional complication for a highly non-uniform beam flux vs. time
- Detailed simulations ongoing, first results are encouraging

## ➤ How to scale to an area $20 \times 20 \text{ cm}^2$

- Beyond the scope of this project







# Thank you



# Spares

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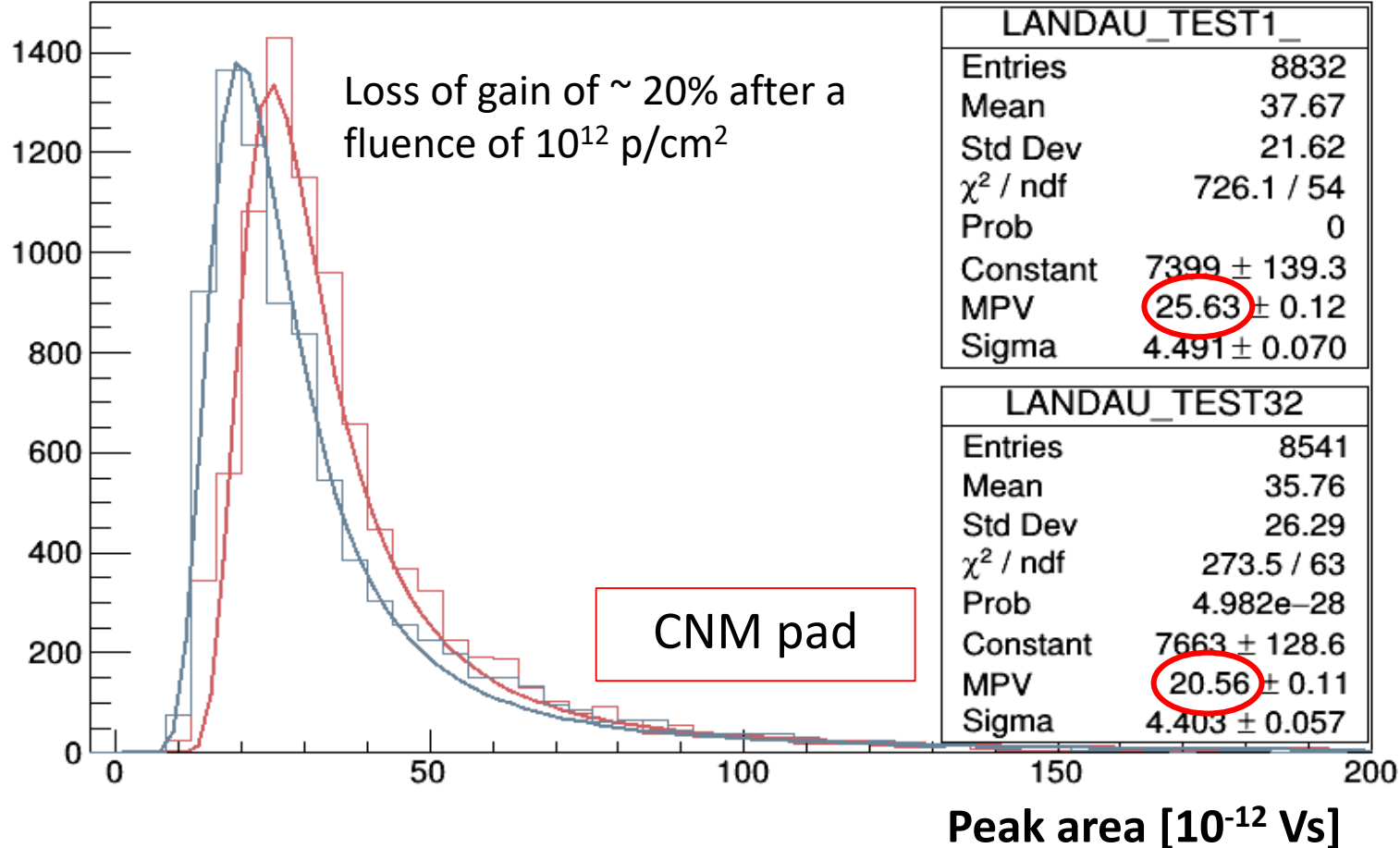


# Concern n.1: effects of radiation damage

Loss of gain of LGADs with radiation reported in literature<sup>1</sup>



Inactivation of the gain layer caused by *acceptor removal* mechanism



1 Kramerger G, et al. 2015 JINST 10 P07006

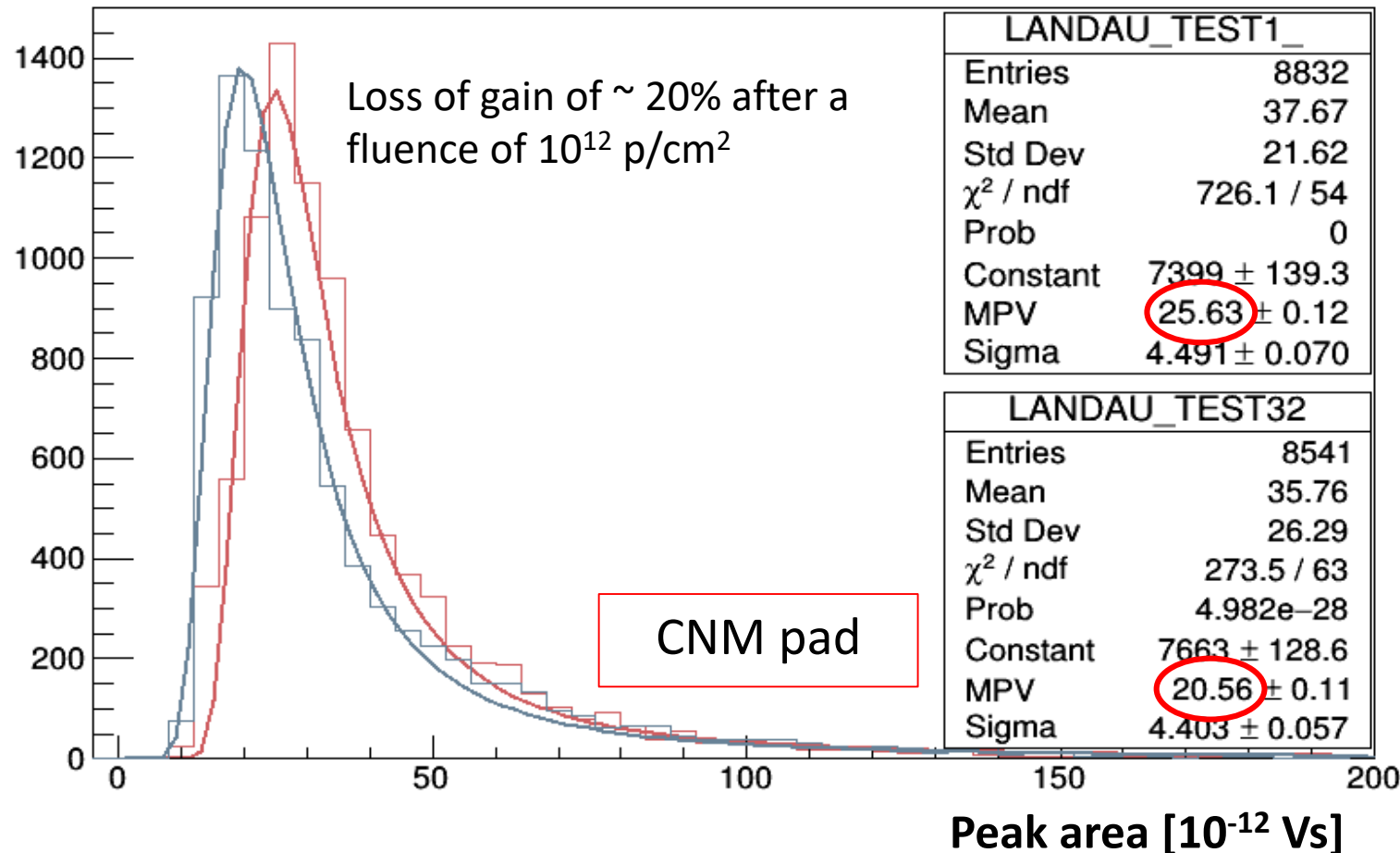


# Concern n.1: effects of radiation damage

Loss of gain of LGADs with radiation reported in literature<sup>1</sup>

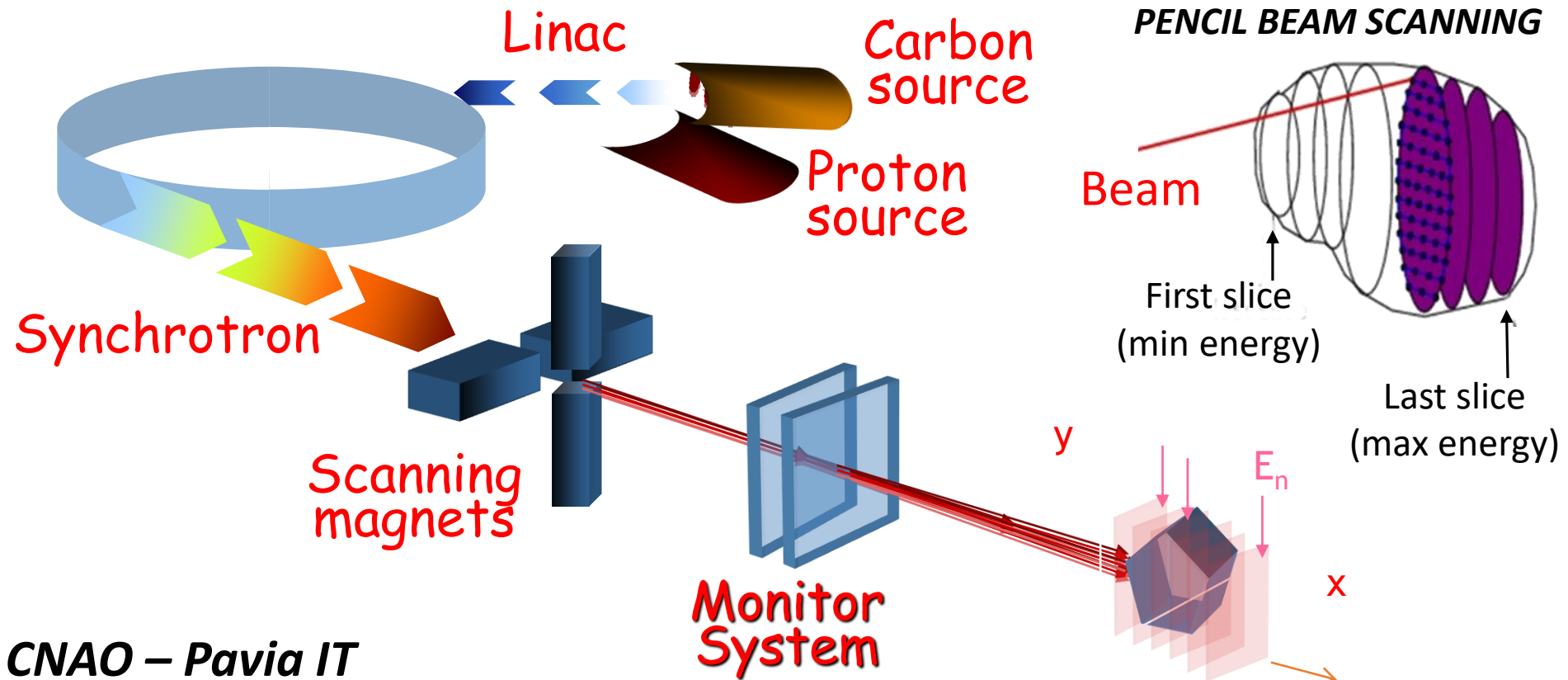


Inactivation of the gain layer caused by *acceptor removal* mechanism



## Note:

- Pad not optimized for radiation resistance, no annealing attempted
- No similar loss observed with Movelt strips

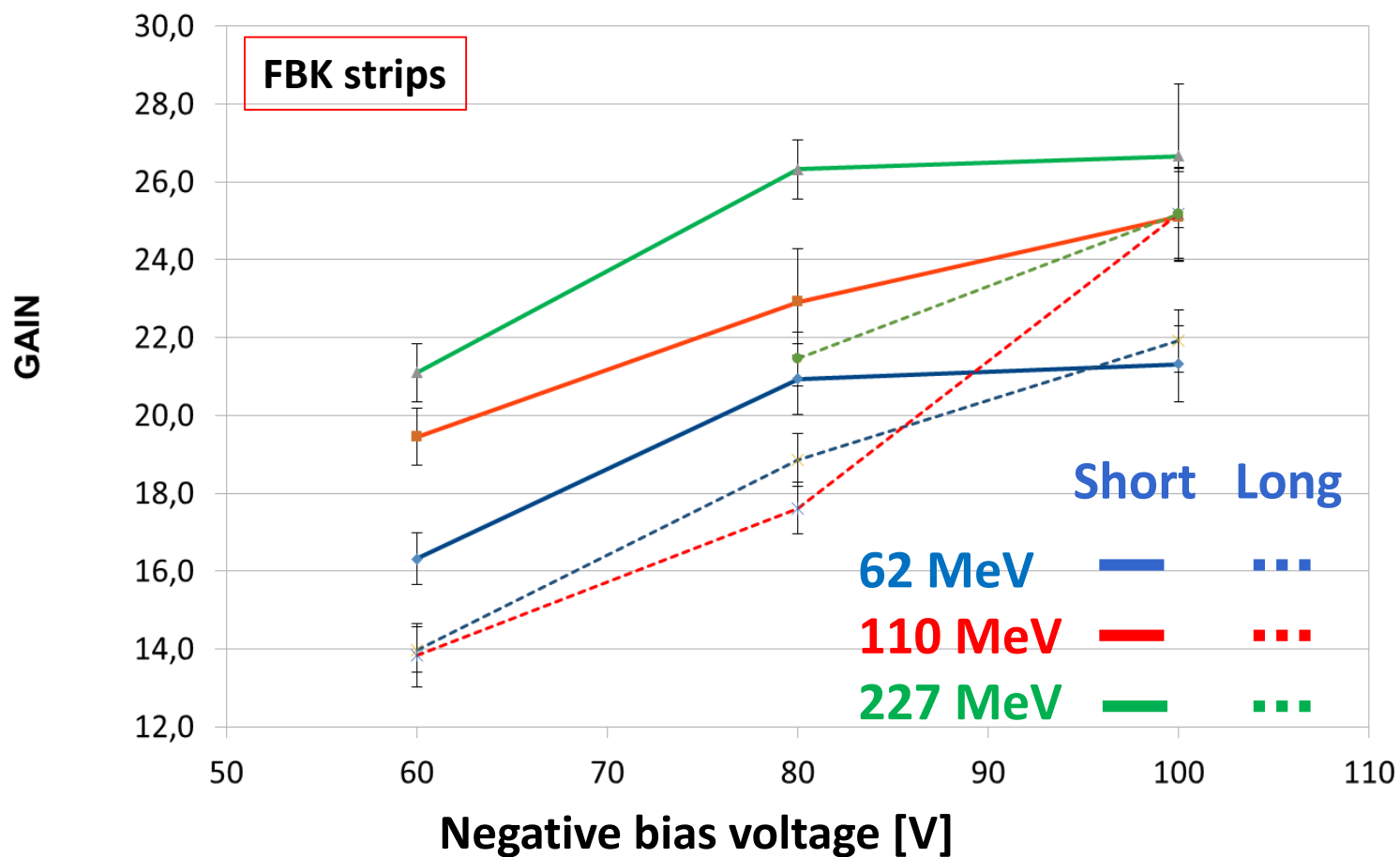


### CNAO – Pavia IT

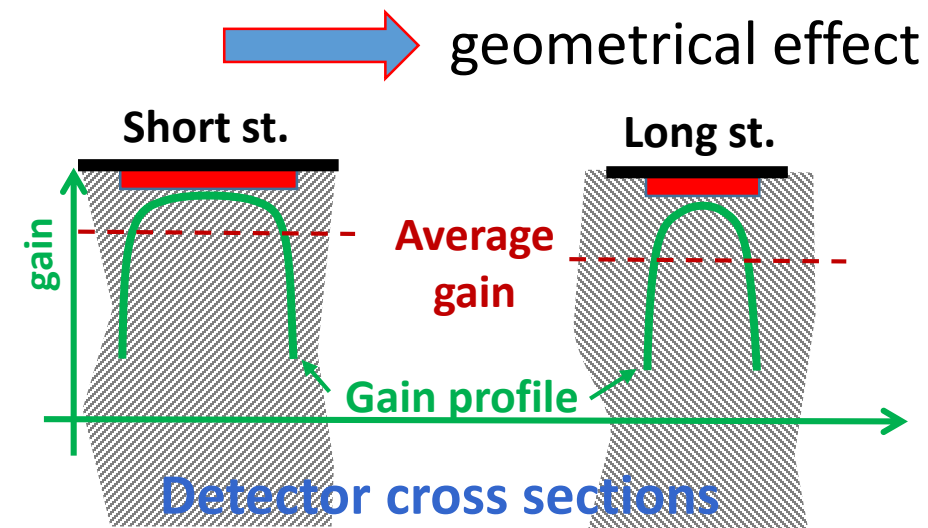
<i>protons</i>	60 - 250 MeV $\sim 10^8$ p/spill
$C^{6+}$	120 - 400 MeV/u $\sim 10^9 - 10^{10}$ p/spill
<i>Range in water</i>	3 - 27 cm

# Gain of strip detectors – Gallium doped

$$\text{Gain(V)} = \frac{\text{MPV}_{\text{gain}} \text{ (V)}}{\text{MPV}_{\text{no gain}} \text{ (V)}}$$

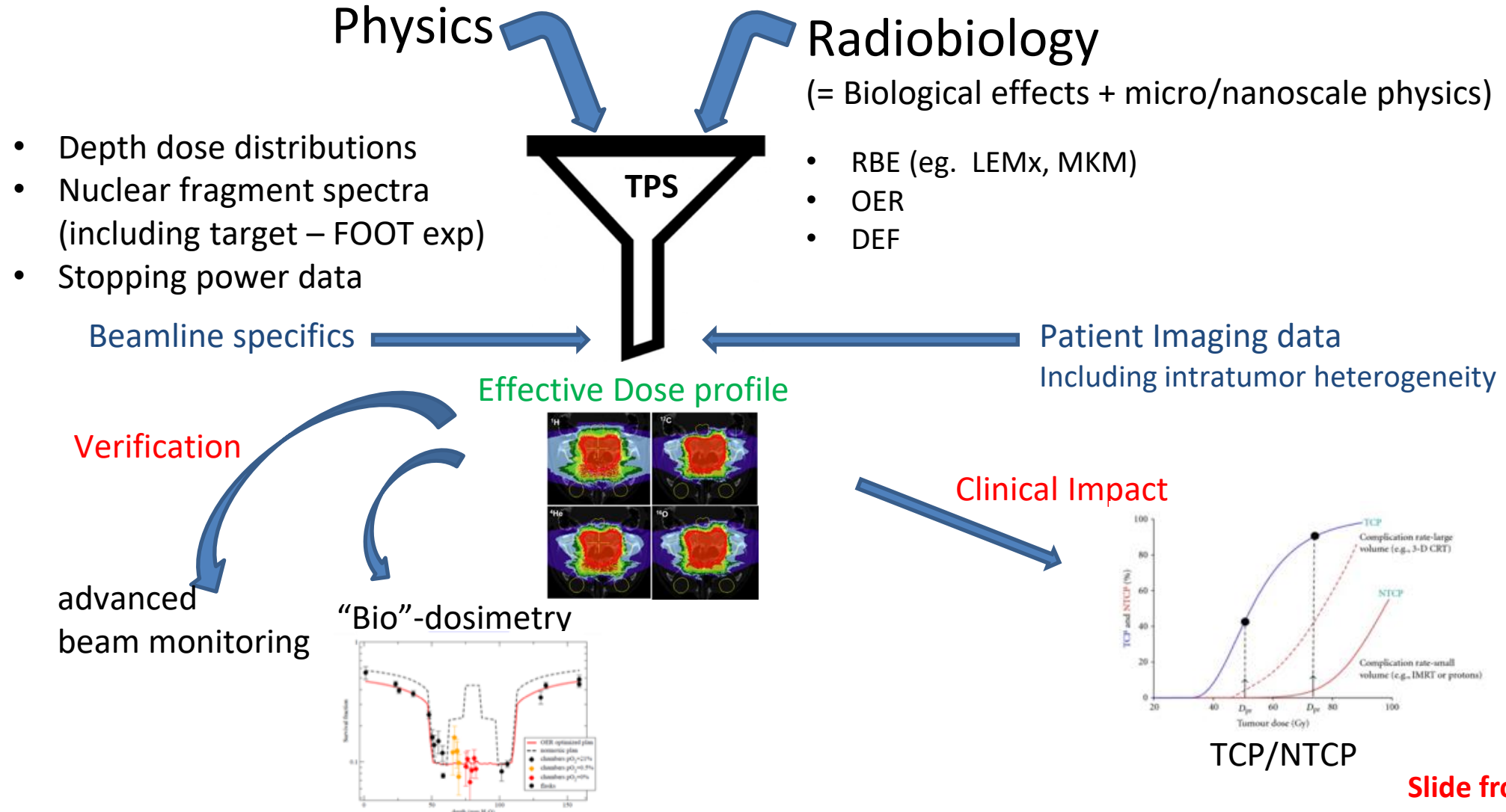


- Gain increase with  $V_{\text{bias}}$
- Similar trend observed with laser source on test pads
- **Long strips** (thinner) show a **lower average gain** than short strips



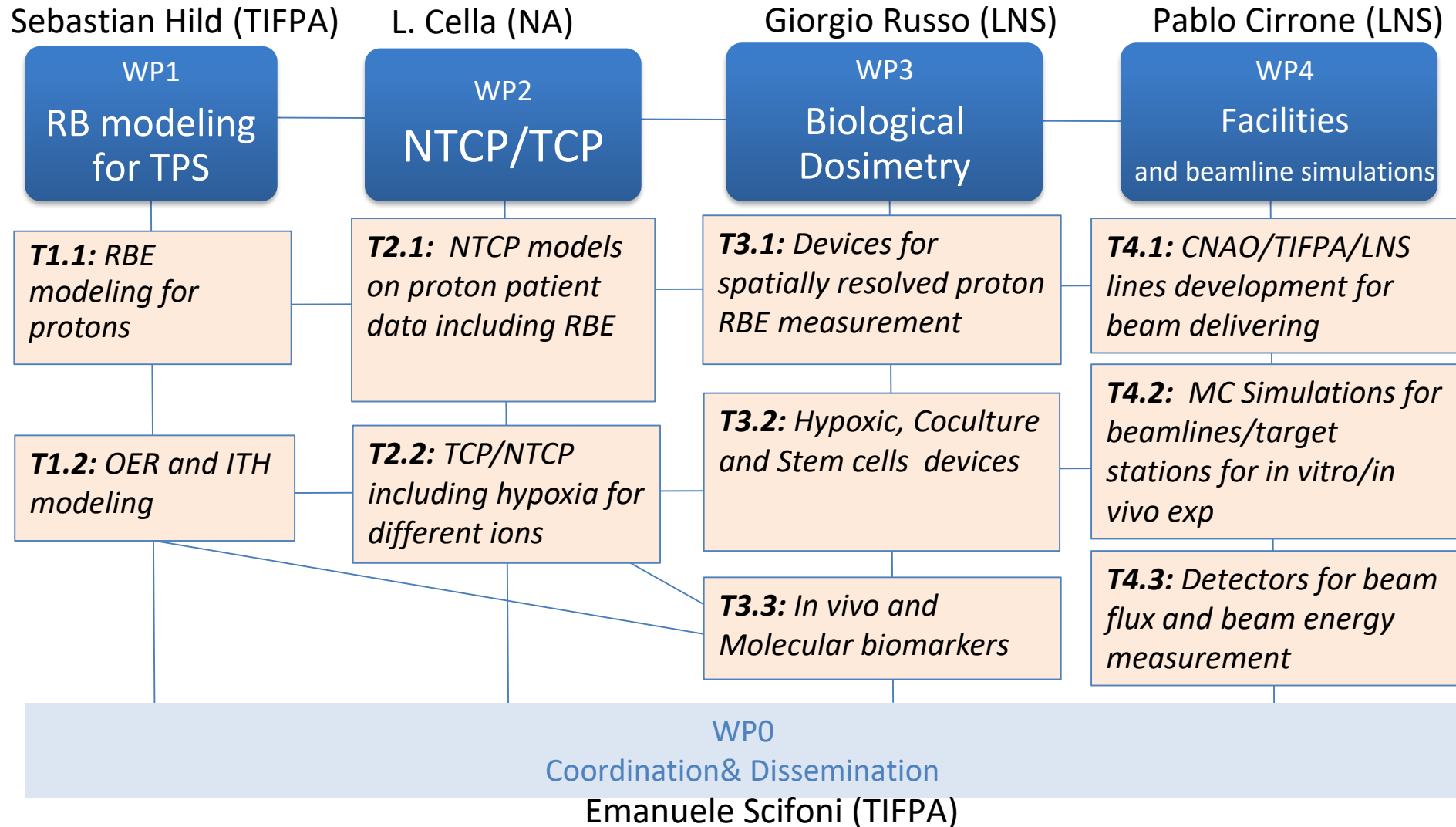


# A Graphical summary of MoVe IT





# MoVe IT - WP Structure and Tasks



# Motivation for the doping strategy of UFSD2 production

Main effect of the irradiation is the inactivation of the dopant in the gain layer

- Substitutional → interstitial (acceptor removal)
- Effect: reduction of gain

## Boron

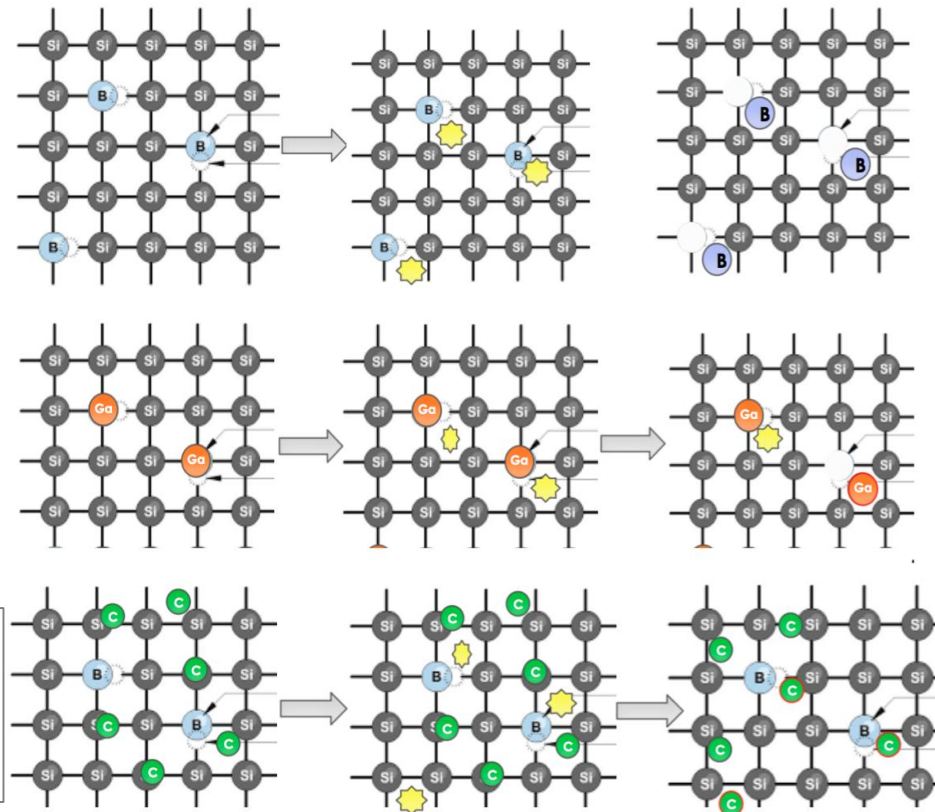
Radiation creates interstitial defects that inactivate the Boron

## Gallium

From literature, Gallium has a lower possibility to become interstitial

## Carbon

Interstitial defects filled with Carbon instead of with Boron and Gallium



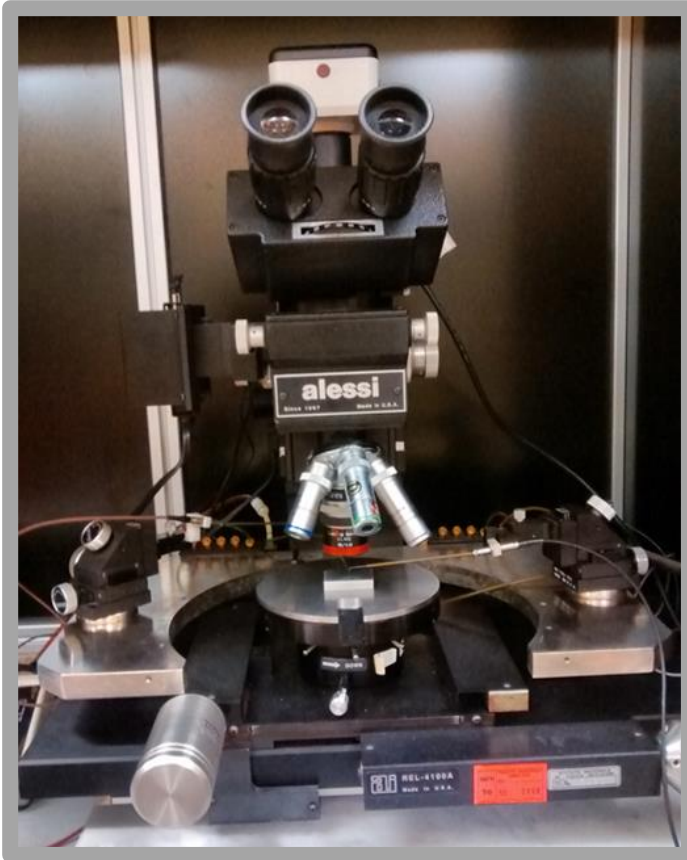
Slide from RD50 Collaboration

## UFSD2 production @ FBK:

- 4 different gain layer strategies:
  - **Boron** (Low & High diffusion)
  - Carbonated **Boron** (High diffusion)
  - **Gallium** (Low diffusion)
  - Carbonated **Gallium** (Low diffusion)
- 4 (3) different **doping concentration** for Boron (Gallium) implants
- 2 different diffusion temperatures for Boron
- 2 carbon concentration (Low & High)

# LAB setup for IV and CV curves

## MANUAL PROBE STATION ALESSI

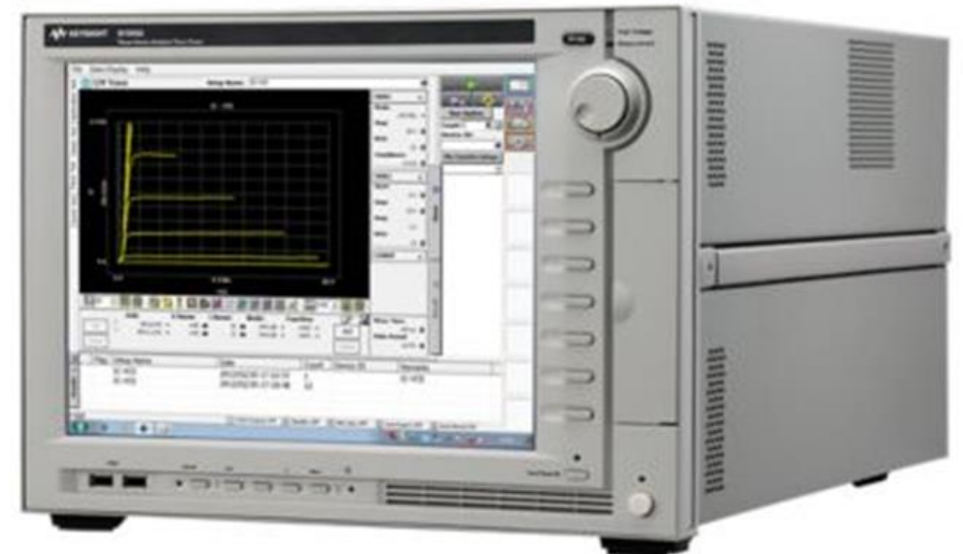


## CUSTOM PROBE CARD FOR SIMULTANEOUS CONTACT TO ALLSTRIPS + GUARD RING

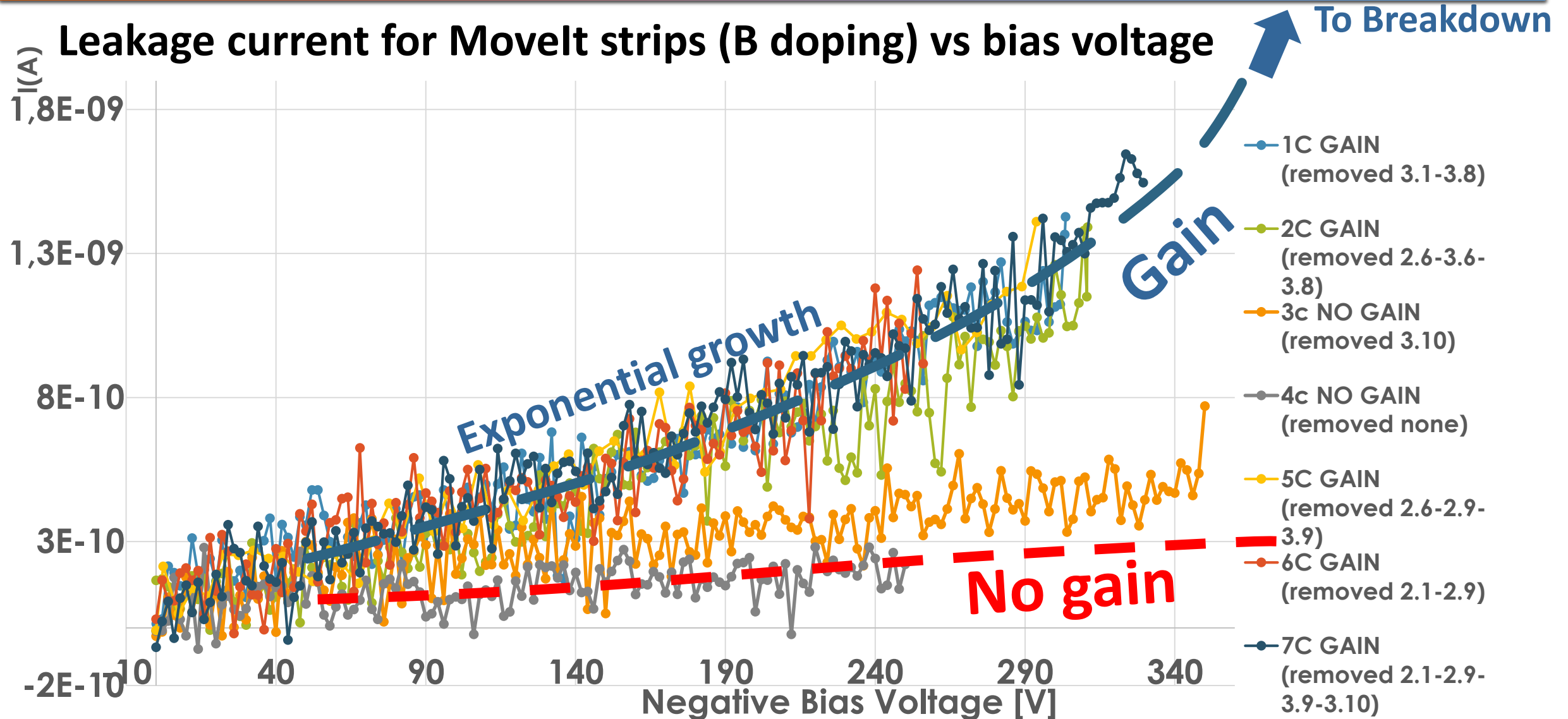


## POWER DEVICE ANALYZER/CURVE TRACKER

MODEL : KEYSIGHT B1505A



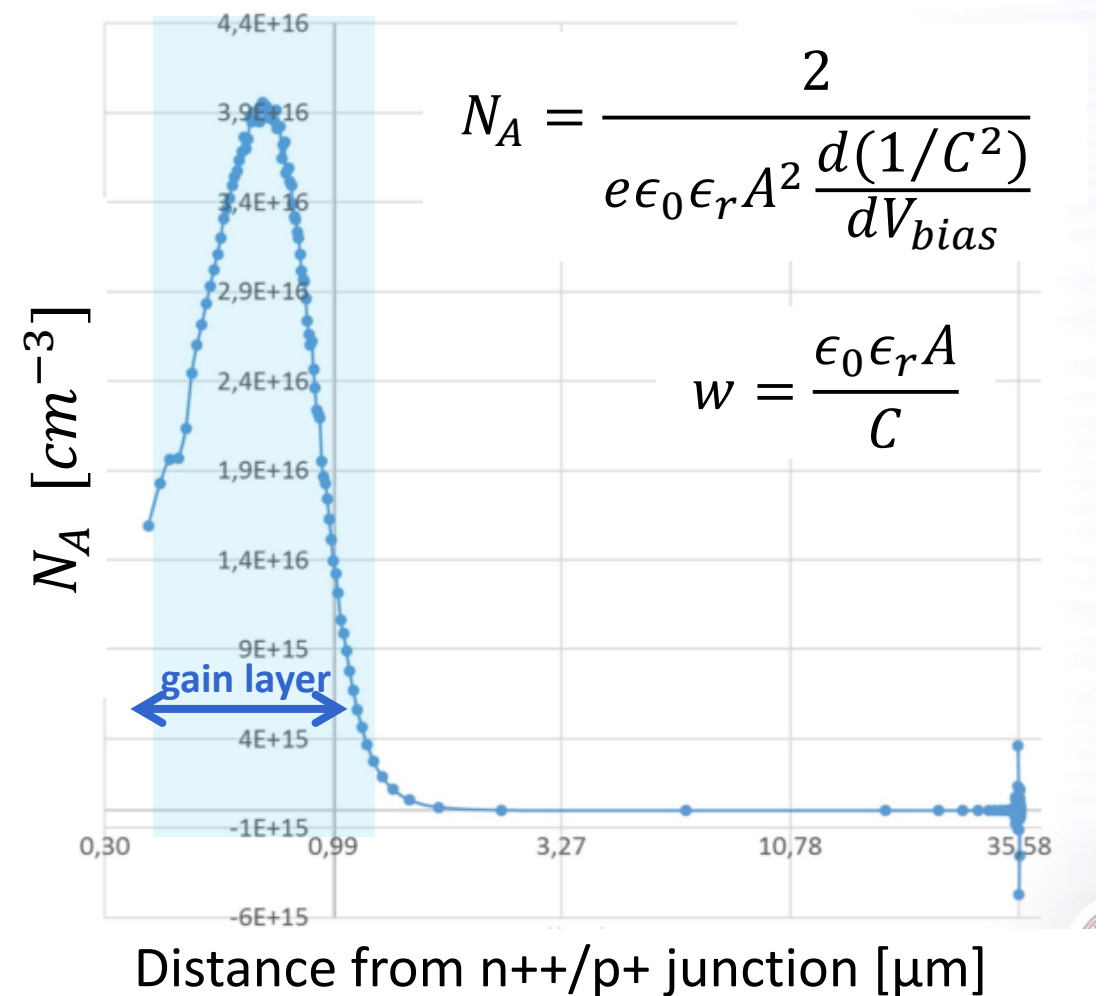
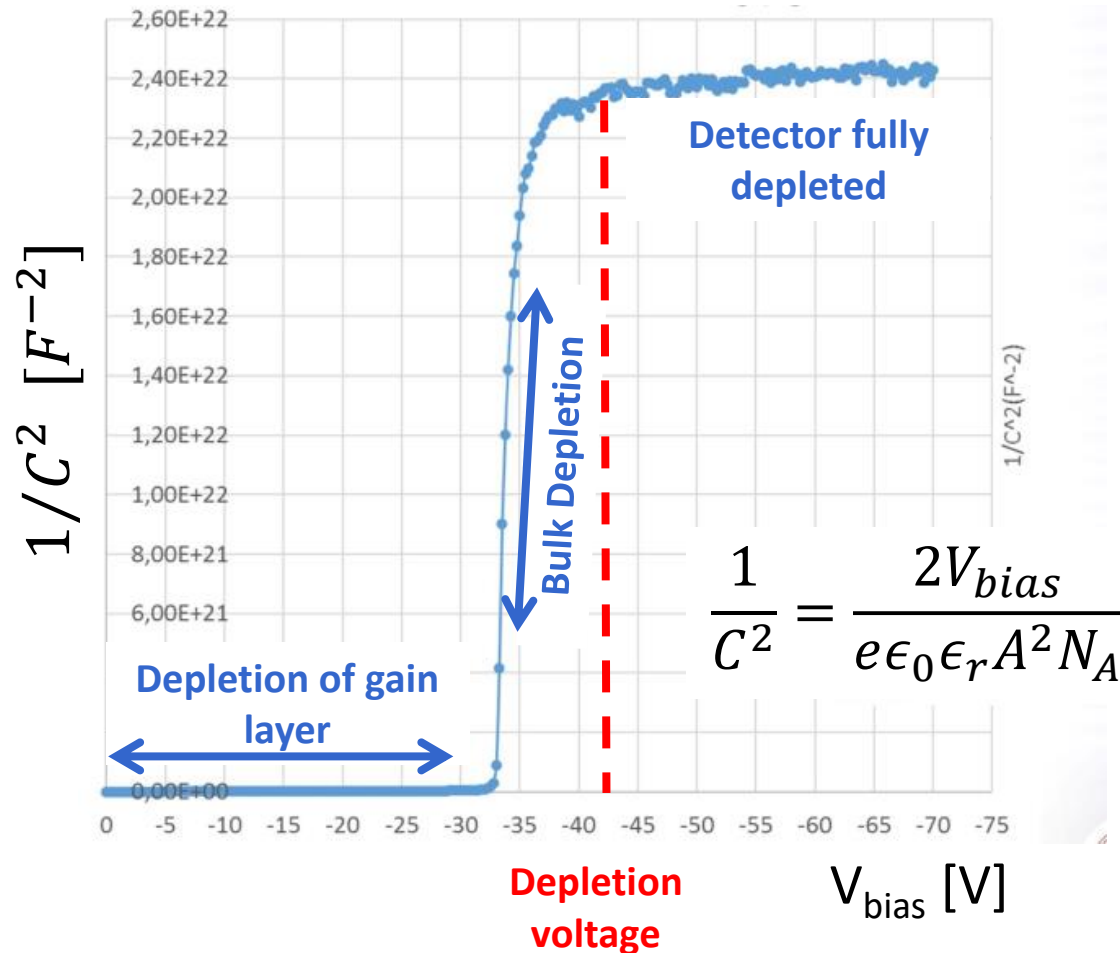
# IV Curves





# CV Curves

Allow to determine the doping profile: example a short Movelt strip (B doped)



# Strip characterization with laser scan

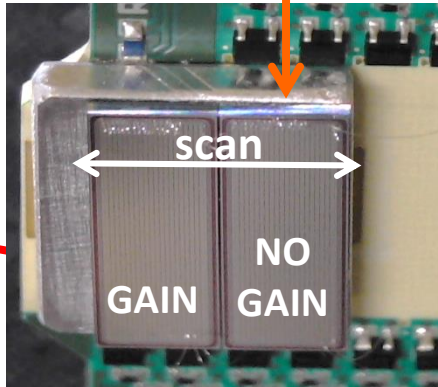
**Picosecond Pulsed IR laser:**

$\lambda = 1060 \text{ nm}$ , Spot size  $\sim 20 \mu\text{m}$

Multichannel Amplifier/Shaper board (CMS CT-PPS)

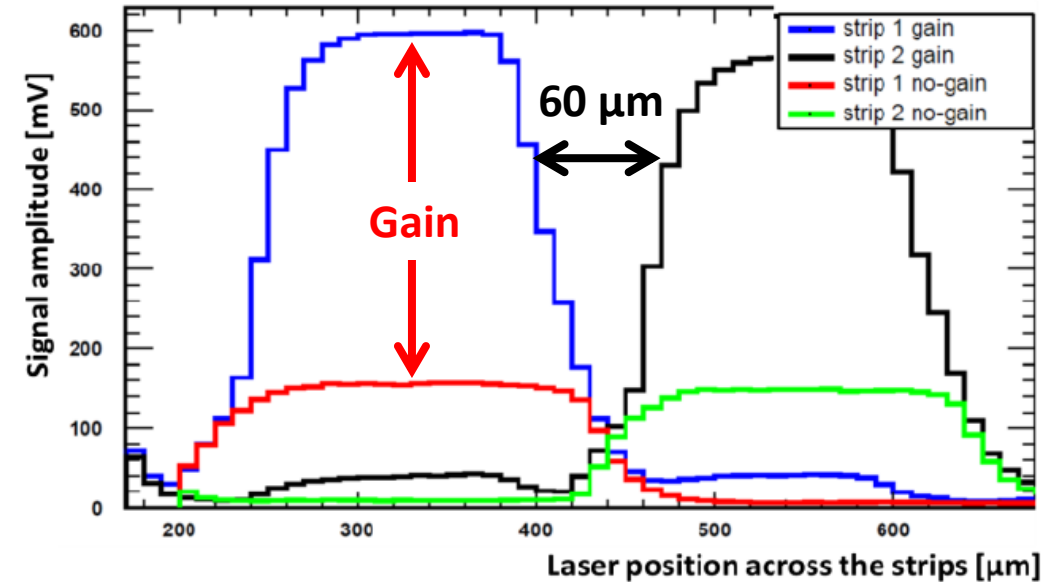
**Front and back metallization:**  
sensor mounted to allow laser scan along the strip edge

Laser beam



Short strips of (B doped)

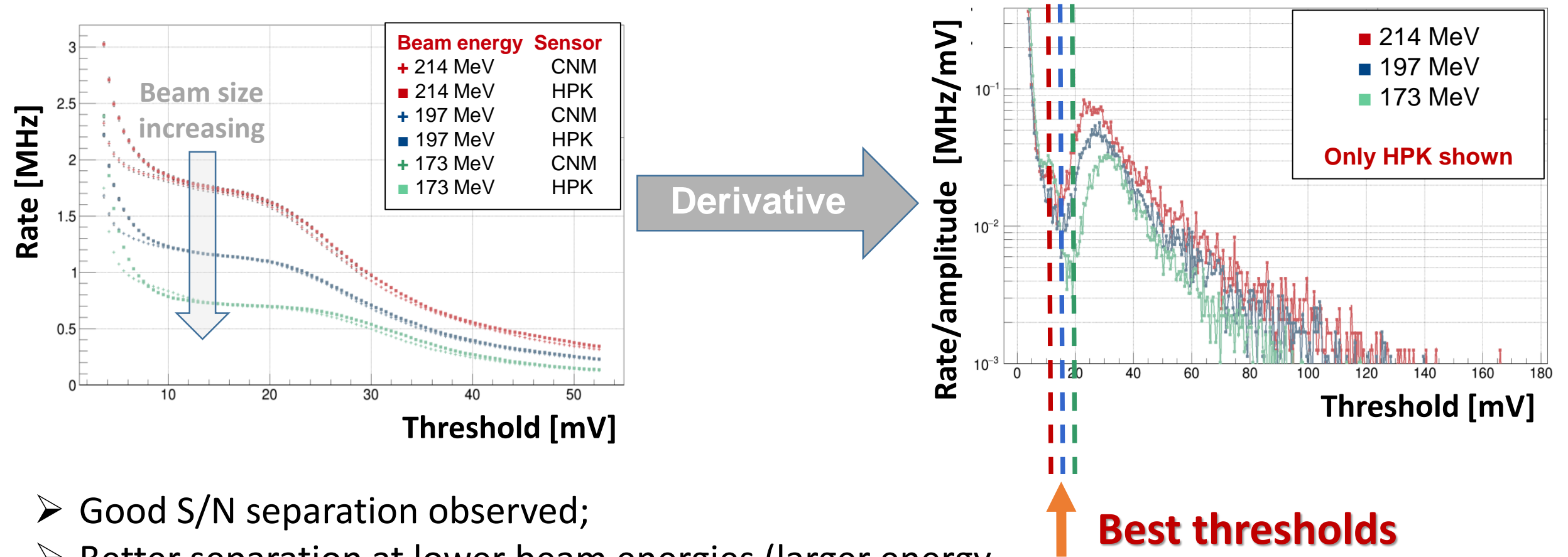
## Signal amplitude scan between adjacent strips



## Results

- **Gain**  $\approx 4$  at  $V_{\text{bias}} = -230 \text{ V}$
- **Dead area**  $\sim 60 \mu\text{m}$ 
  - expected by sensor layout and by the production technology, in agreement with TCAD simulations
  - possibly reduced in next UFSD production

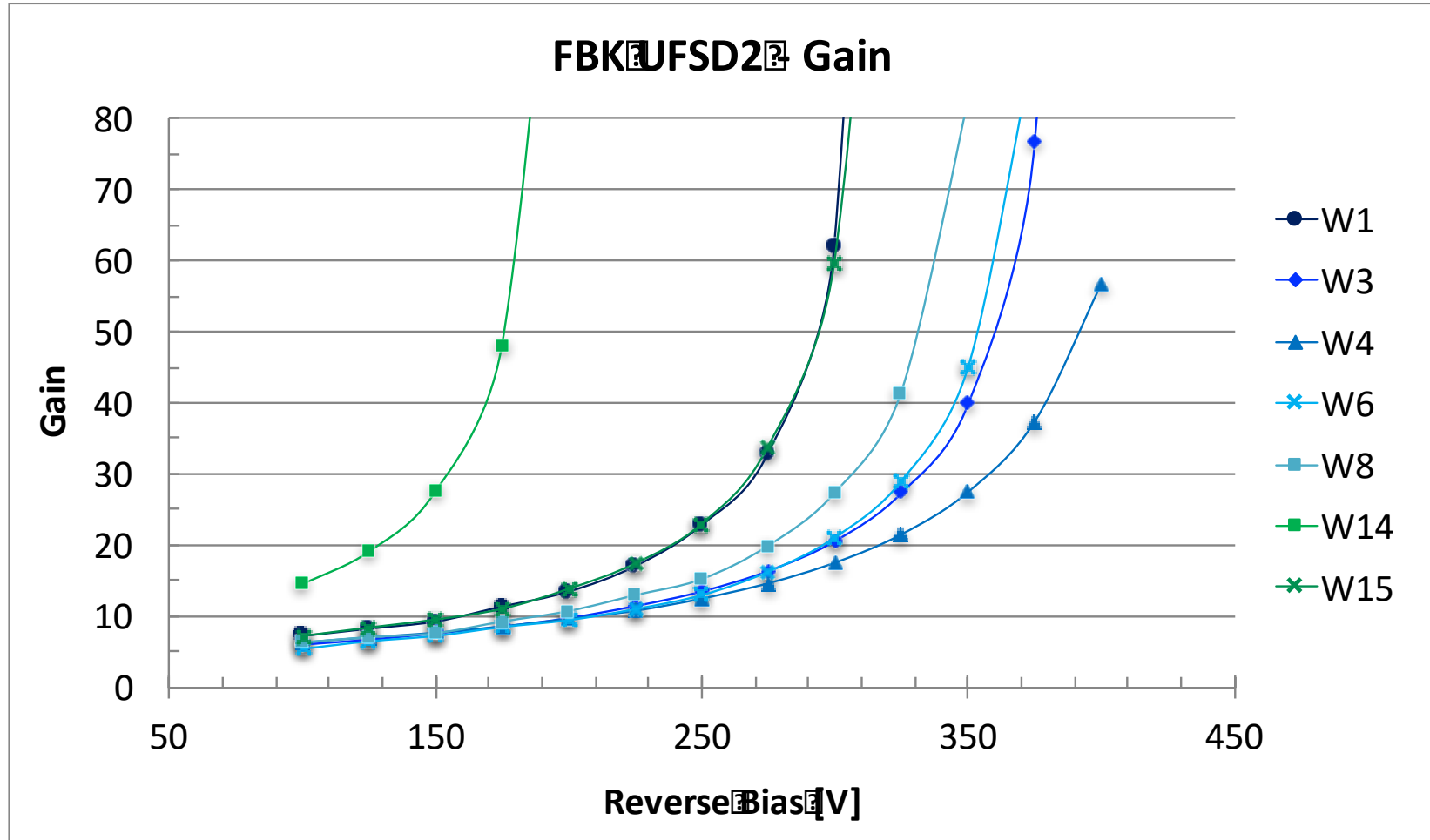
# Threshold scan



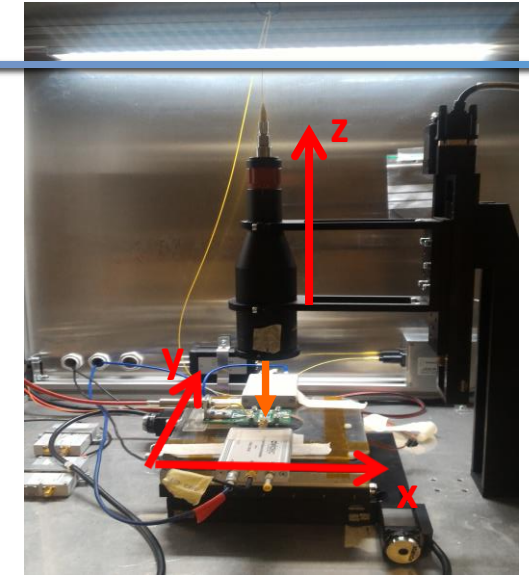
- Good S/N separation observed;
- Better separation at lower beam energies (larger energy loss in Silicon):
- Best threshold is beam energy dependent



# Gain Measurement with PS laser



$$GAIN = (Signal\ area\ LGAD) / (Signal\ area\ PiN)$$



## TCT Setup from Particulars

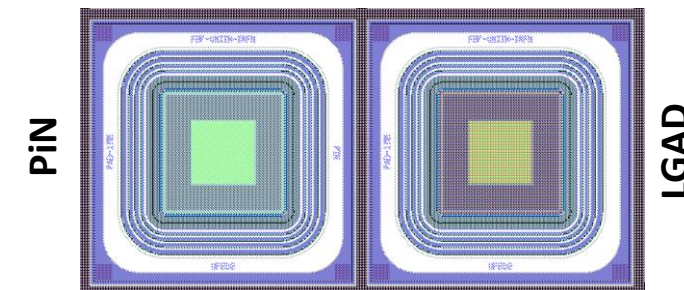
Pico-second IR laser at 1064 nm

Laser spot diameter ~ 50 μm

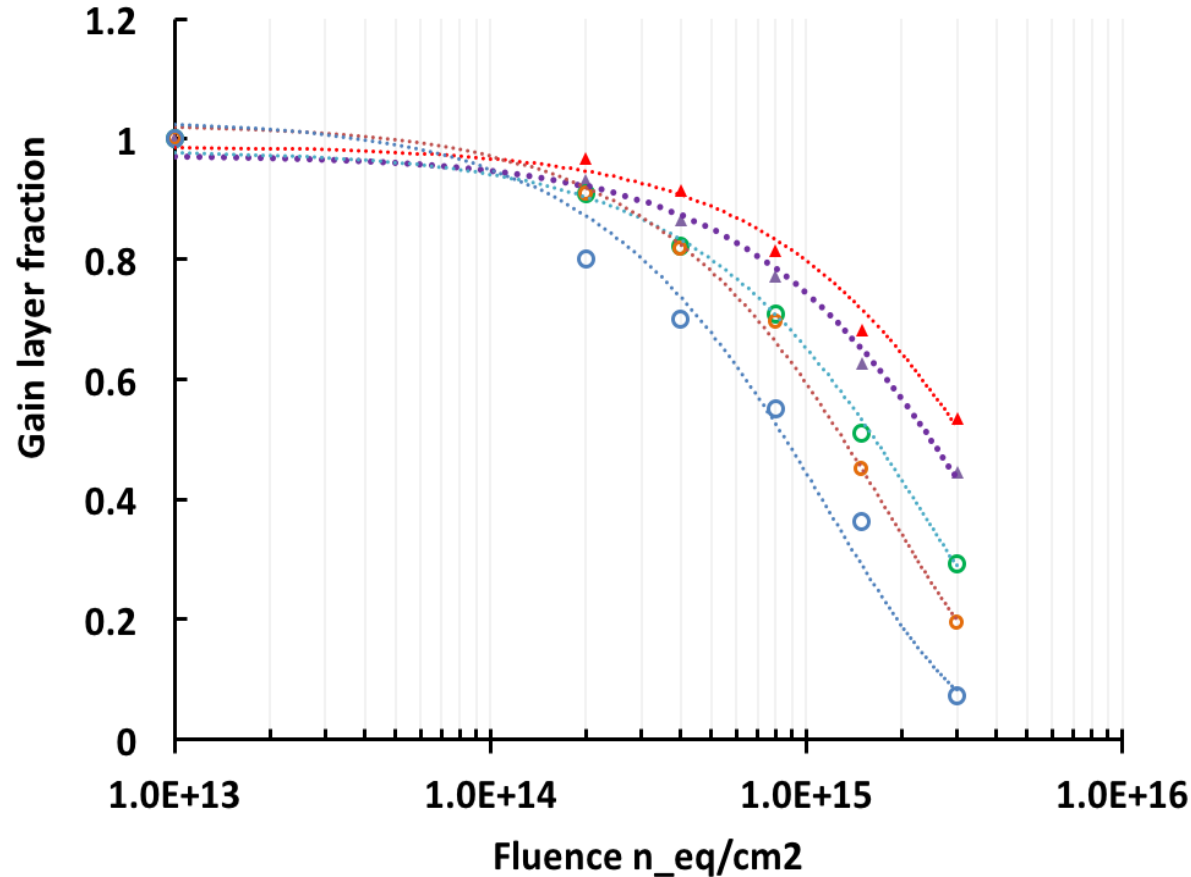
Cividec Broadband Amplifier (40dB)

Oscilloscope Lecroy 640Zi

Room temperature



# Irradiation with neutrons



$$y = 9.9E-01e^{-2.1E-16x} \quad \blacktriangle W6 \text{ B+C} - \langle CV \rangle$$

$$y = 9.7E-01e^{-2.7E-16x} \quad \blacktriangle W15 \text{ Ga+C} \langle CV \rangle$$

$$y = 9.8E-01e^{-4.1E-16x} \quad \circ W1 \text{ LD} \langle CV \rangle$$

$$y = 1.0E+00e^{-5.5E-16x} \quad \circ W8 \text{ B} \langle CV \rangle$$

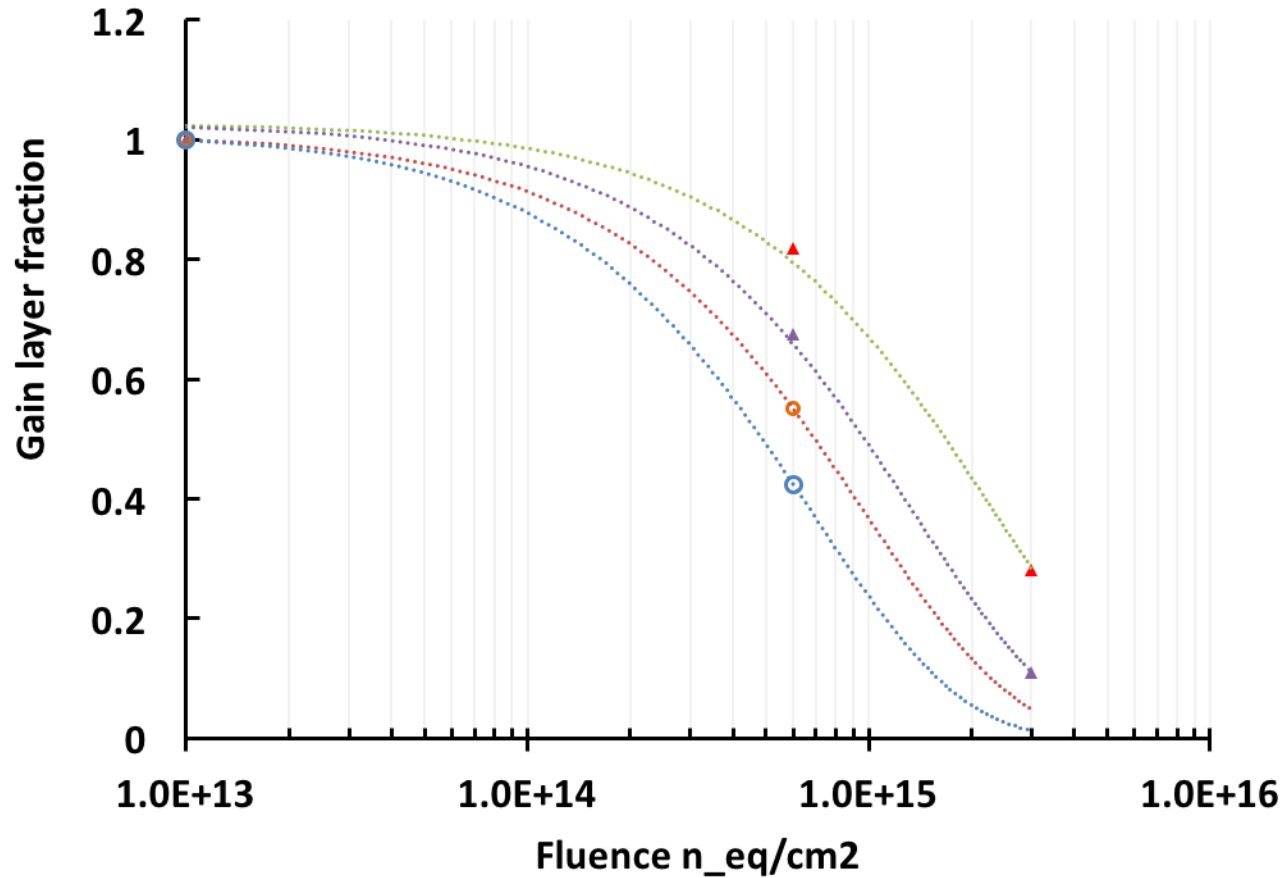
$$y = 1.0E+00e^{-8.5E-16x} \quad \circ W14 \text{ Ga} \langle CV \rangle$$

Irradiation in Ljubljana

Fluence steps:  $2 - 4 - 8 \cdot 10^{14} n_{eq}/cm^2$   
 $1.5 - 3 - 6 \cdot 10^{15} n_{eq}/cm^2$   
 $1 \cdot 10^{16} n_{eq}/cm^2$

- ▷ Carbonated sensors have a factor  $\sim 3$  better acceptor removal coefficient
- ▷ Among not carbonated sensors, low diffusion Boron has the better response to irradiation

# Irradiation with protons



$$y = 1.0E+00e^{-4.3E-16x} \quad \blacktriangle \text{ W6 B+C - <CV>}$$

$$y = 1.0E+00e^{-7.4E-16x} \quad \blacktriangle \text{ W15 Ga+C <CV>}$$

$$y = 1.0E+00e^{-1.0E-15x} \quad \bullet \text{ W3 B <CV>}$$

$$y = 1.0E+00e^{-1.5E-15x} \quad \bullet \text{ W14 Ga <CV>}$$

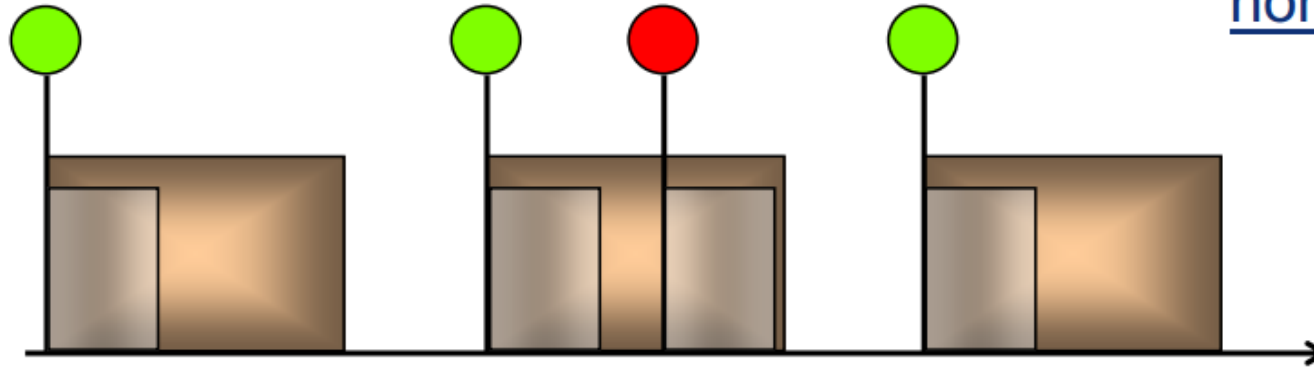
24 GeV/c Proton irradiation @ CERN PS

Fluence steps: 1 -  $6 \cdot 10^{14} n_{eq}/cm^2$

1 - 3 - 6 -  $9 \cdot 10^{15} n/cm^2$

# Pileup Models

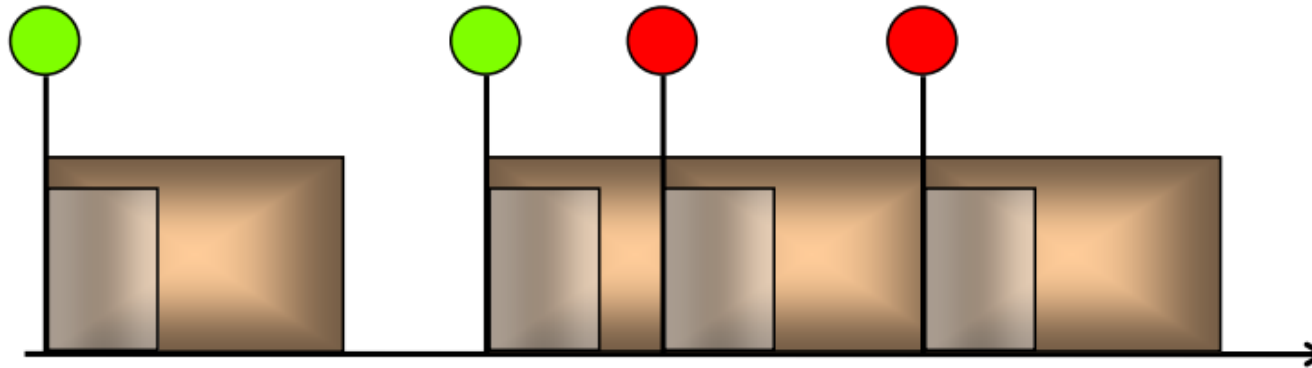
## Non-paralyzable model



non-extending dead time

$$R = \frac{\rho}{1 + \rho\tau_{ne}}$$

## Paralyzable model

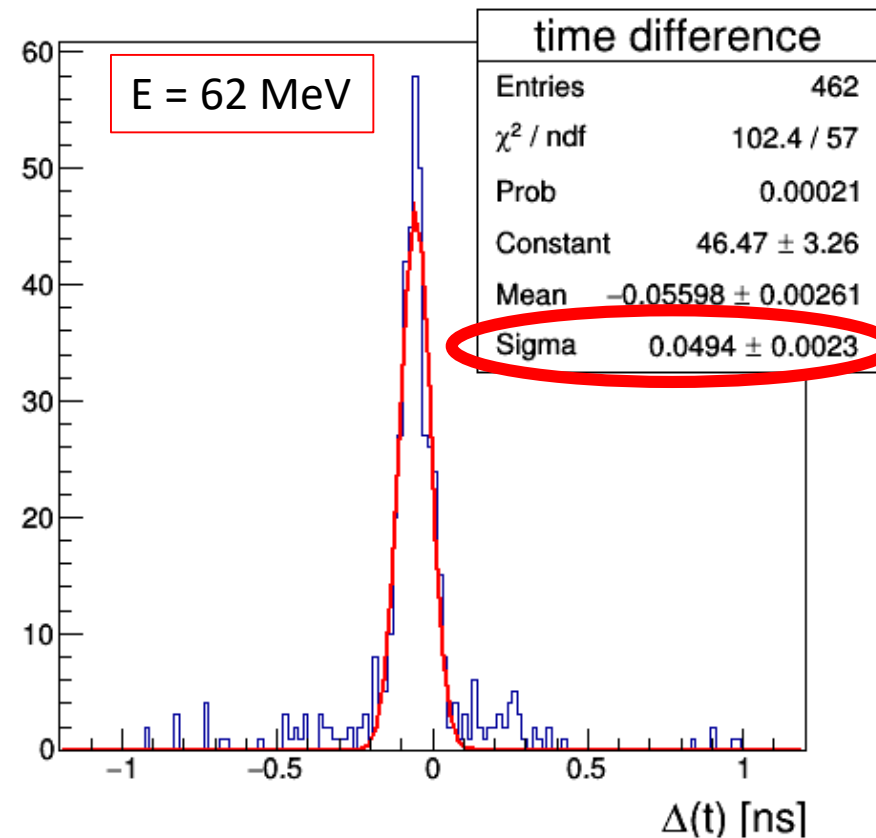


extending dead time

$$R = \rho e^{-\rho\tau_e}$$

# Best time resolution

- CFD algorithm applied on pulses signals
- Time difference measured for pulses in coincidence in the 2 pads



Time resolution of single crossing

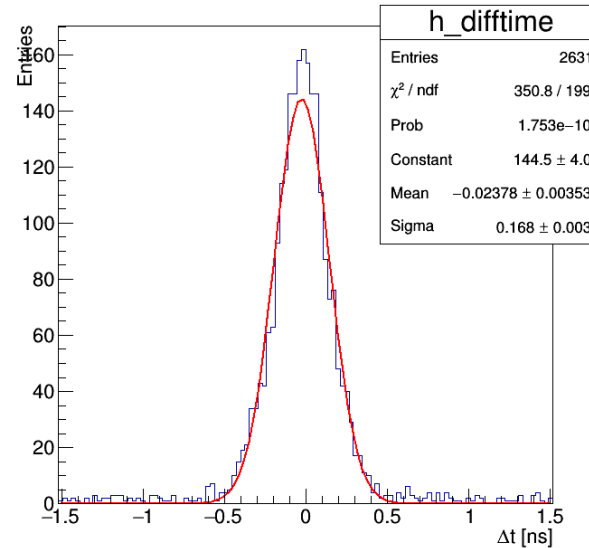
➡  $\sigma(t) = 35 \text{ ps} !!$

# ToF measurement with different algorithms

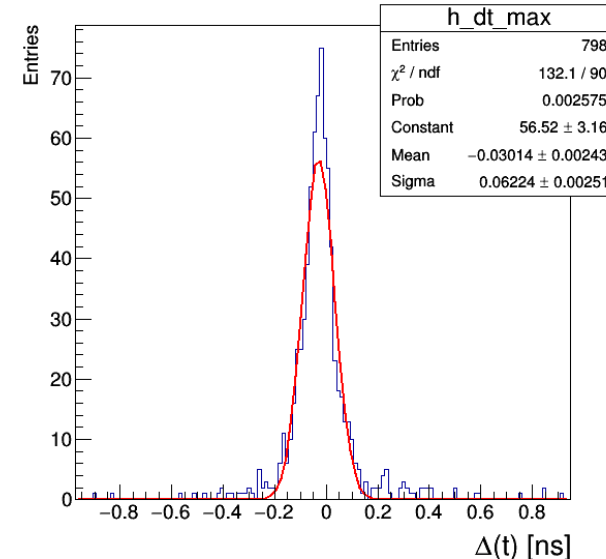
From test beam data:

- Beam  $E = 117$  MeV
- **total acquisition time 300  $\mu$ s** (less than average spot duration)
- 3 ToF reconstruction methods

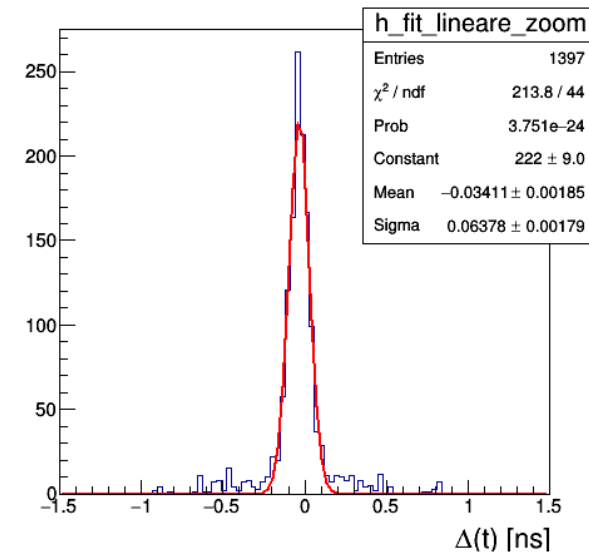
**LE** - leading edge  
(fixed threshold)



**CC** - Maximization of cross-correlation function of two digitizer waveforms



**CFD** - Constant Fraction Discriminator



Algorithm	Mean $\Delta t$	$\Delta t$ resolution
LE	- (24 $\pm$ 3) ps	170 ps
CC	- (30 $\pm$ 2) ps	62 ps (snapshot)
CFD	- (34 $\pm$ 2) ps	64 ps

Remarks

- Sensors at 2cm distance (favorable condition)
- Ongoing simulations for optimizing the geometry

# Simulation of UFSD beam telescope

**GEANT4** simulation of material effects (energy loss and multiple scattering)

**WEIGHTFIELD2** simulation of the UFSD response.

$$f = 10^9 \text{ p}/(\text{s} \cdot \text{cm}^2)$$

$$T_{\text{acquisition}} = 200 \text{ } \mu\text{s}$$

## Error on mean $\Delta t$ vs distance

$E = 60 \text{ MeV}$ , Window = 200 ns, n.loops = 1000

Thickness = 50  $\mu\text{m}$ , Fix threshold

